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The Leaders in Silicon Photomultipliers Since 2004

SensL Technology Update

Institute of Nuclear Research, April 2014

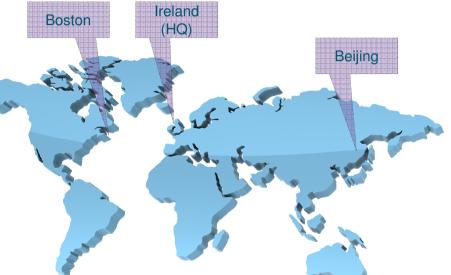
Seminar Overview

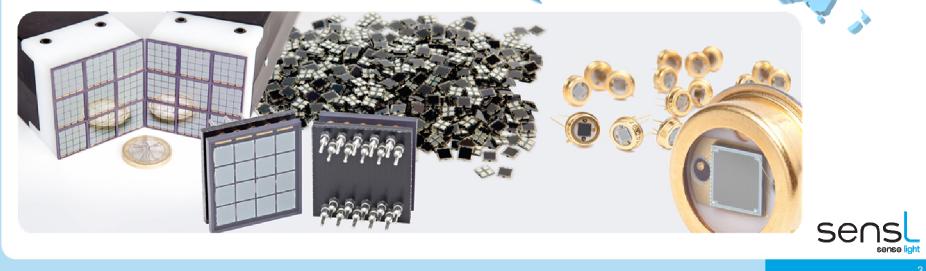
- SensL Company Overview
 - History
 - Core value proposition
- SensL Silicon Photomultiplier (SiPM) Technology Overview
 - Low light sensing & technology evolution
 - Current technology status
- Products & Pricing Overview
- Applications Overview
 - Nuclear Medicine, LiDAR, Radiation Detection, Industrial, Automotive
- Supply Chain Overview



SensL Quick Facts

Business	Low Light Silicon Sensors	Boston
Markets	Medical Imaging Radiation Detection Automotive & Industrial Biophotonics, HEP, Academic	
Model	Fabless Semiconductor	





SensL Company History

- Pre-2004: Initial research at Tyndall National Institute, Cork
- 2004: SensL founded, HQ in Cork
- **2005**: Photon counting products & modules
- 2006-2007: "A-Series" 1st Generation SiPM
- 2008: Array-2 Introduced
- 2009: Array-4 Introduced
- **2010**: Transfer to commercial 8" CMOS foundry
 - Second generation of silicon ("L-Series")
 - Matrix9 Introduced
- 2011: Third generation of silicon ("M-Series")
 - Large area arrays (Array-8)
- 2012: Surface-mount (SMT) devices introduced -High speed output introduced
- 2013: Fourth generation of silicon ("B-series") introduced
 SMT Arrays introduced







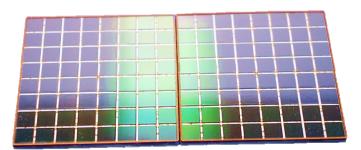
Low Light Sensor Leadership

SensL is the leading developer of Silicon Photomultiplier (SPM) technology manufactured in standard CMOS foundries to replace the aging industry standard Photomultiplier Tube (PMT)



SensL Uniquely Enables:

High Performance Uniformity Large Area Form Factor Flexibility Low Cost



Photomultiplier Vacuum Tube SensL Silicon Photomultiplier





Low Light Sensing –

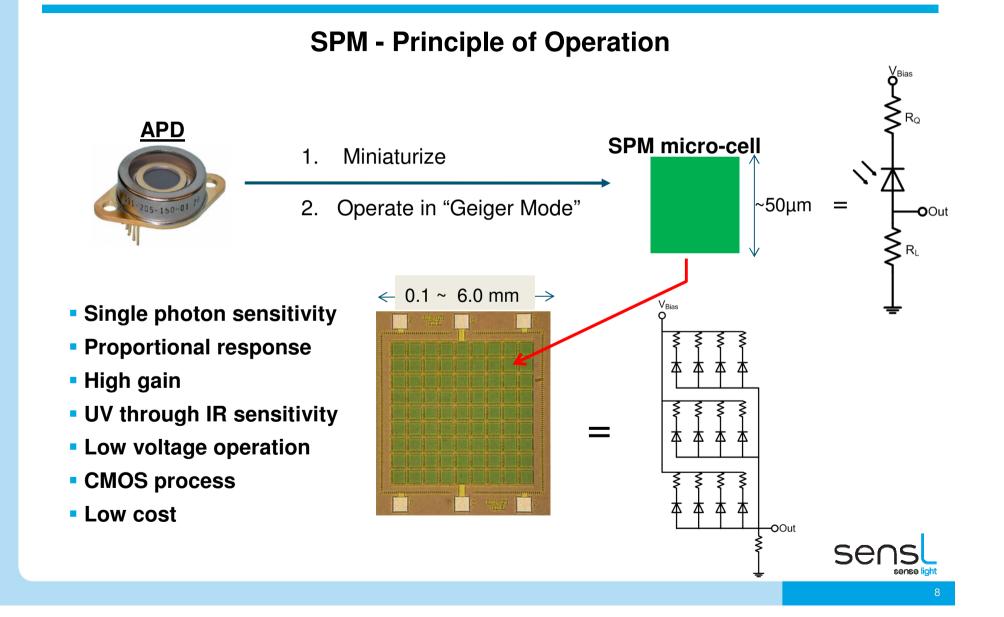
Technology Evolution & Update

SensL SiPM

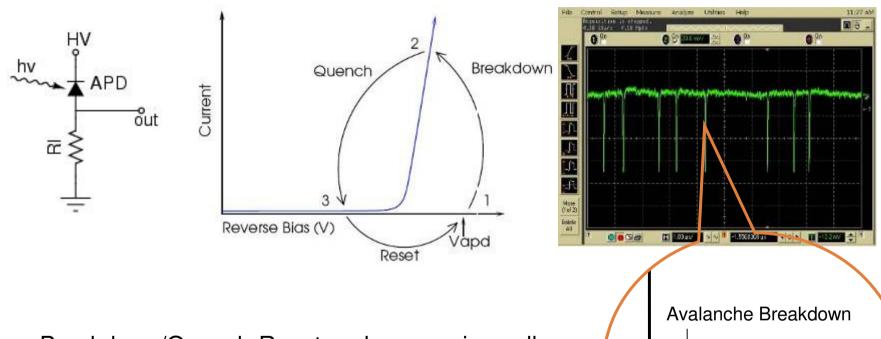
- What is an SiPM?
 - Array of Geiger-mode photon sensors optimized for gain and high speed
- Advantages of SiPM over PIN or APD
 - Gain of SiPM is >1M
 - Output response is picoseconds
 - Temperature stability
 - Uniformity of output response
 - Wide dynamic range
 - Large area array compatible
 - CMOS compatible



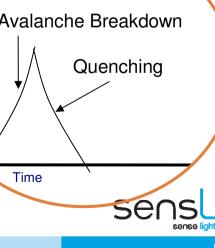
Silicon Photomultipliers



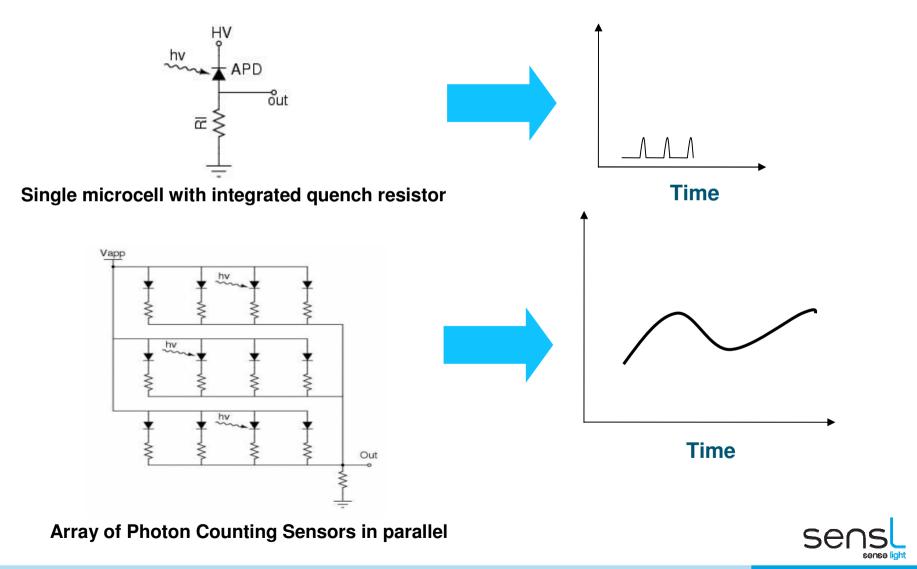
Geiger Mode Operation



- Breakdown/Quench-Reset cycles per microcell
- Output is a pulse of charge for each photon
- All SensL devices operate <30V



SiPM Concept



Sensor Technology Comparison

	PIN	APD	PMT	SiPM
Gain	1	10 ²	10 ⁶	10 ⁶
Operating Voltage	0V to 5V	100V to 1kV	800V to 1kV	30 V
Temperature Sensitivity	Low	High	Low	Low
Mechanical Robustness	High	High	Low	High
Damage by Stray Light	No	Yes	Yes	Νο
Spectral range	UV-VIS-NIR	UV-VIS-NIR	Blue/UV	UV-VIS-NIR
Readout Electronics Complexity	Complex	Complex	Simple	Simple
Form Factor	Small	Small	Bulky	Small
System Cost	Medium	Medium	High	Lowest
Scalable Technology	Yes	Νο	No	Yes
Electromagnetic Immunity	Νο	No	Νο	Yes
Sensor Noise	Low	Med	Low	Lowest
Response time	Fast	Slow	Fast	Fastest

SiPM provides highest performance and lowest system cost





Current Technology

M & B Series Overview

Technology Spotlight

L Series

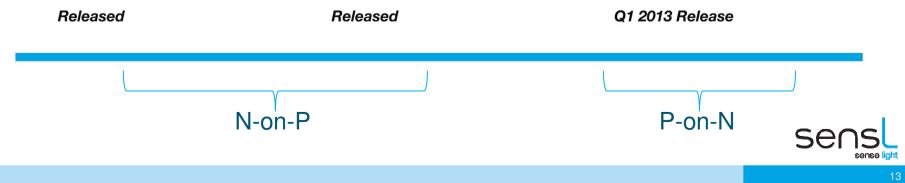
- » Base Technology
- » 495nm peak sensitivity

M Series

- » Improved PDE
- over L Series
- » 495nm peak sensitivity
- » High Resolution timing using fast output*

B Series

- » Maximum PDE and fast timing
- » 420nm peak sensitivity
- » High Resolution timing*



Terminology

•<u>M-Series</u> - A family of SiPM products based upon a N-on-P structure, featuring a third terminal that carries a *fast output*.

•<u>B-Series</u> - A family of SiPM products based upon a P-on-N structure, featuring a third terminal that carries a *fast output*.

•<u>FM</u> - An M-Series SiPM product that has at least 3 pins (or pads) accessible that include *anode*, *cathode* and the *fast output* and can therefore be used in fast mode configuration

•<u>FB</u> - A B-Series SiPM product that has at least 3 pins (or pads) accessible that include *anode*, *cathode* and the *fast output* and can therefore be used in fast mode configuration

•<u>SM</u> - An M-Series SiPM housed in a 2-pin package that only gives access to the *anode* and *cathode*. The third terminal (fast output) is not accessible, and so SM sensors can only work in standard mode.

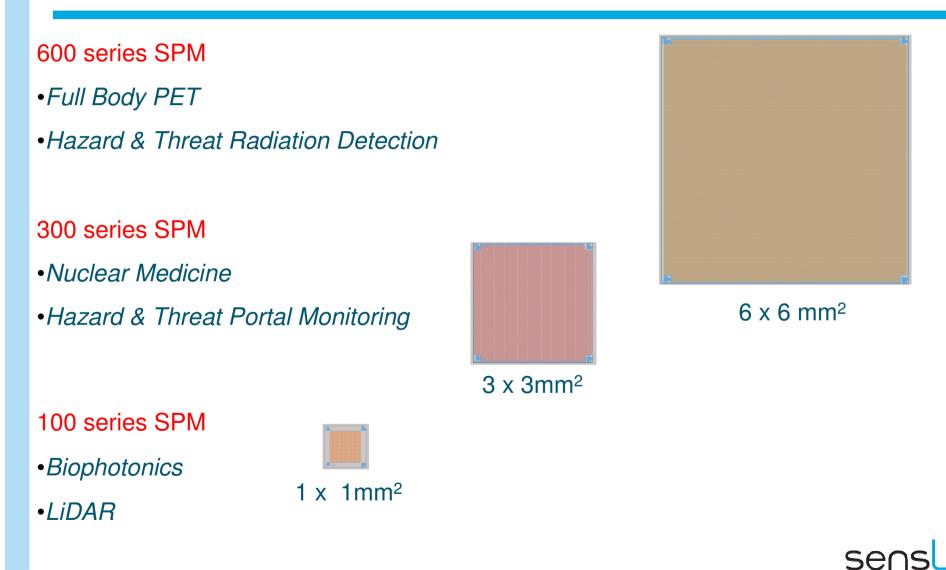
•<u>SB</u> - A B-Series SiPM housed in a 2-pin package that only gives access to the *anode* and *cathode*. The third terminal (fast output) is not accessible, and so SB sensors can only work in standard mode.

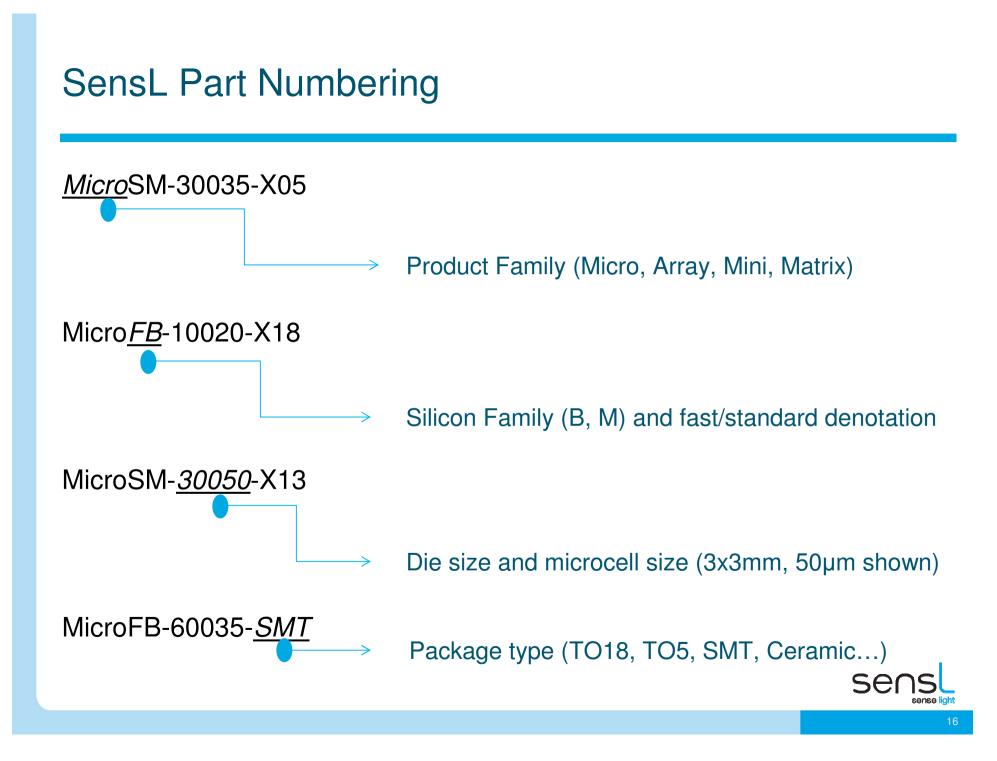
•<u>Fast mode</u> - Using the *fast output* signal from an FM or FB product.

-<u>Standard mode</u> - Using only the *anode* and *cathode* of either an M or B product where the *fast output* terminal is not connected.

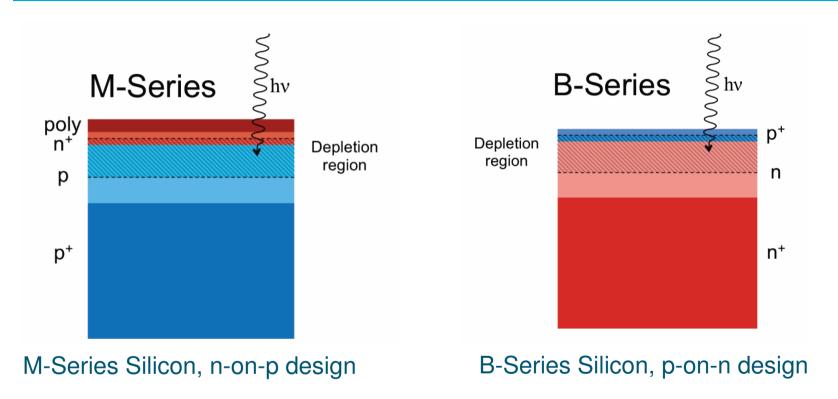


SiPM Product Pixel Dimensions





Detector Architecture



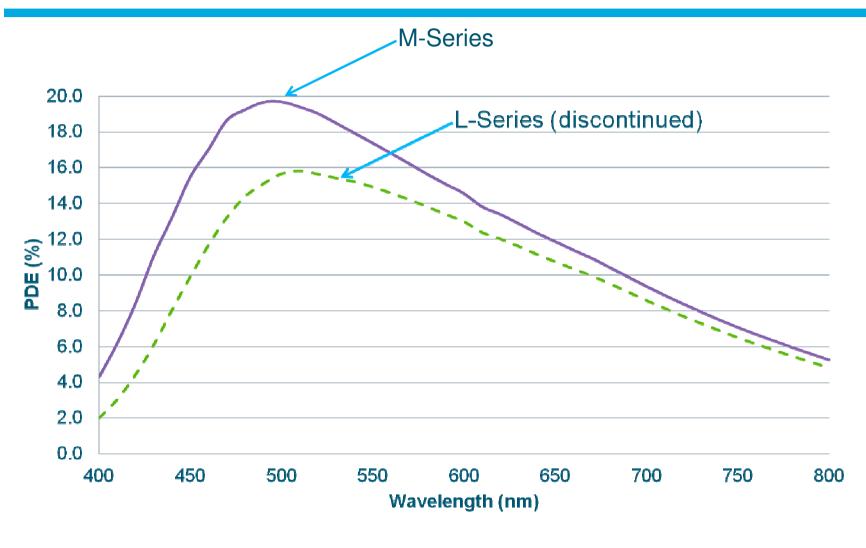
The M-series (and now discontinued L-Series) use an n-on-p junction design giving peak photon detection efficiency (PDE) centered around 500nm producing a green-sensitive device.

The B-Series is based on a p-on-n junction which makes the device more suited to shorter wavelengths – it's peak response is at 420nm producing a more blue-sensitive device

This presentation will concentrate on the B-Series



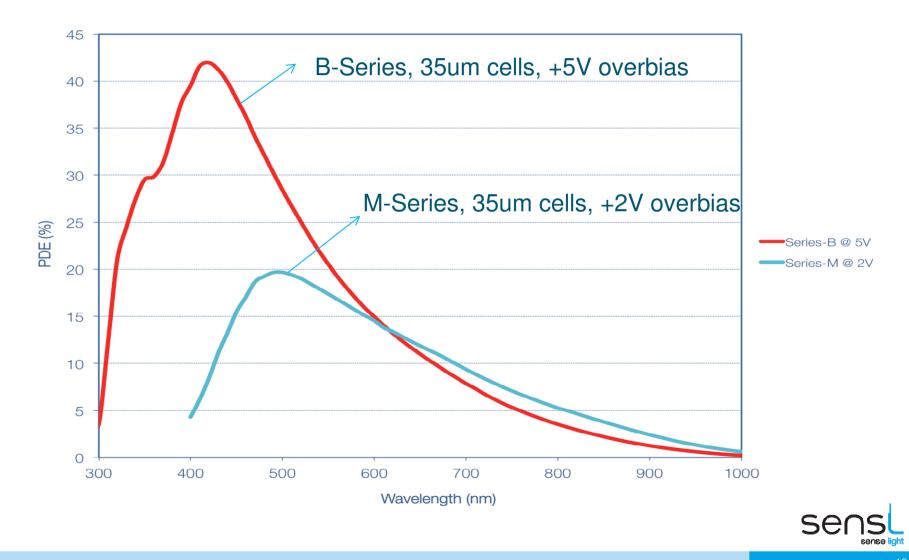
L-Series & M-Series PDE Comparison



Both curves are for 35um cells at +2V overbias



B-Series & M Series PDE Comparison





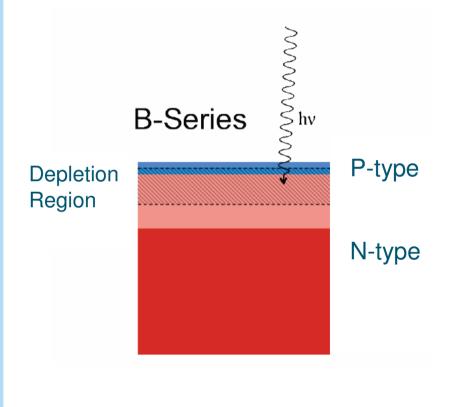
B Series Characteristics

Datasheet Plots Production Silicon Revision



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B Series Technology:



P on N technology provides the highest levels of Blue and UV photon sensitivity Compatible with Fast Output (3-terminal) & Standard Output (2-terminal)

Cathode

Anode

sense liot

ser

Fast Output

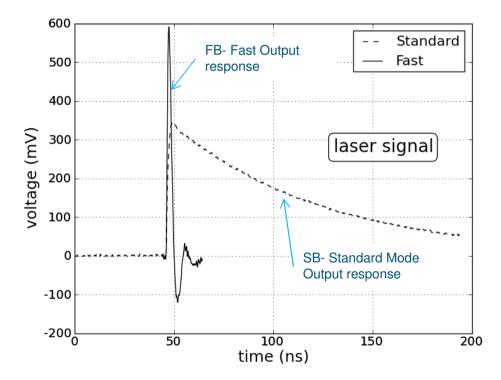
Fast Output Advantages

Fast Mode Improvements

Rise times <100ps; 2ns recovery
Short impulse response from 1-2ns
FWHM

Reduced signal output capacitance
Higher count rate resolution ability
Ability to clearly distinguish the first photon arrival time

SiPM Type	Fast Output Rise Time	Fast Output Signal Pulse Width (FWHM)
10035	300ps	600ps
30020	501ps	1310ps
30035	609ps	1510ps
30050	638ps	1480ps
60035	884ps	3180ps

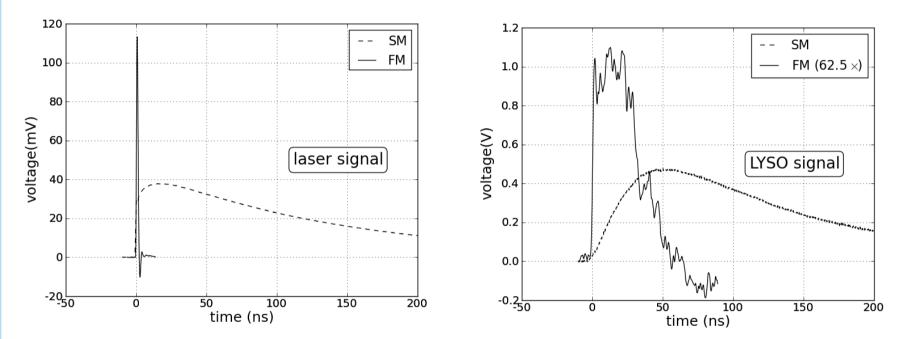


SensL's international patent application no. WO2011117309



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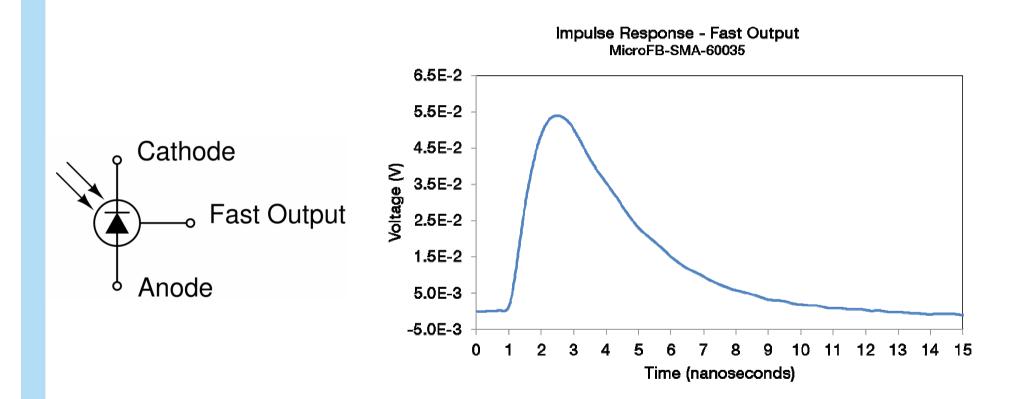
F-Detectors – Fast SPM for Improved Timing



- Significantly faster output signals:
 - rise times 100ps 2ns (size dependant)
 - fast decay times
 - optimal for timing applications
 - provides higher count rates
 - ability to distinguish the first photon
- Data published at Photodet2012 (June 2012)

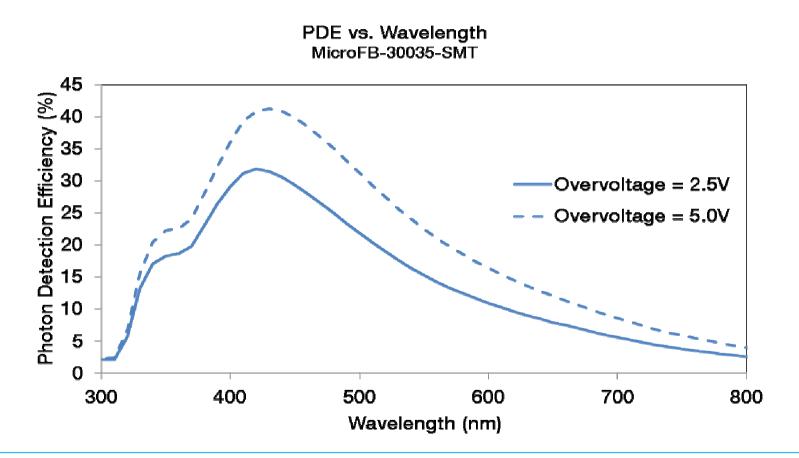


Pulse Shape 6mm Sensor – Fast Output



Low capacitance Fast Output Capable (35um cell shown)

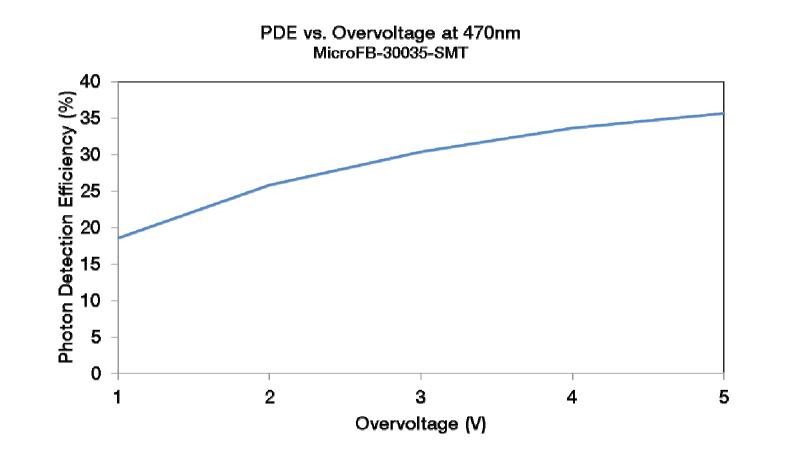
PDE Vs. Wavelength



PDE optimised for fast blue/UV scintillators (35um cell shown)

SEAS

PDE vs. Overvoltage



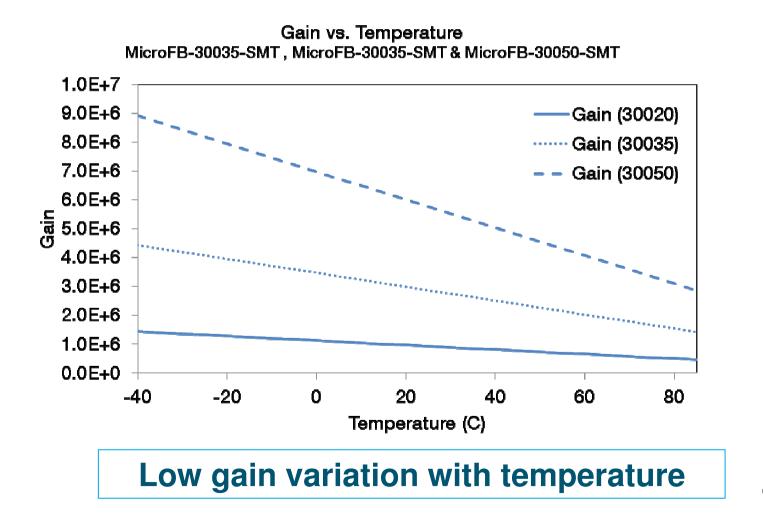
PDE optimisation with overvoltage (35um cell shown)

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sense light

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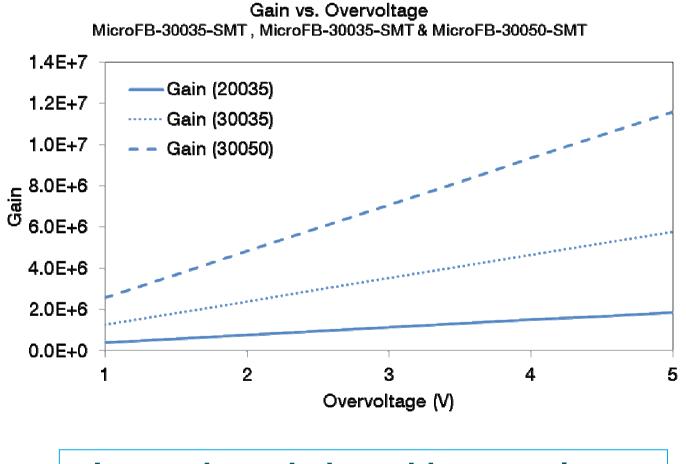
Gain vs. Temperature



Sense

Proprietary and Confidential

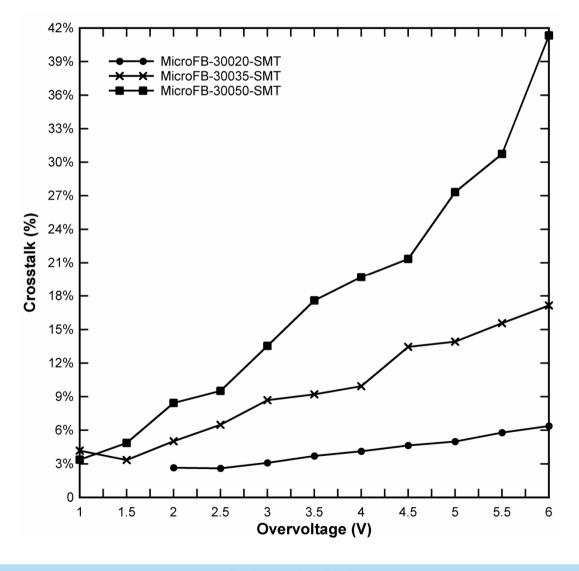
Gain vs. Overvoltage



Low gain variation with overvoltage



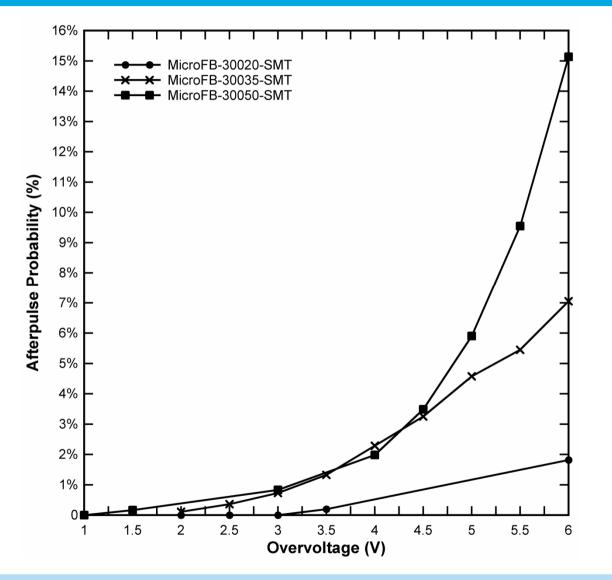
Crosstalk vs. Overvoltage





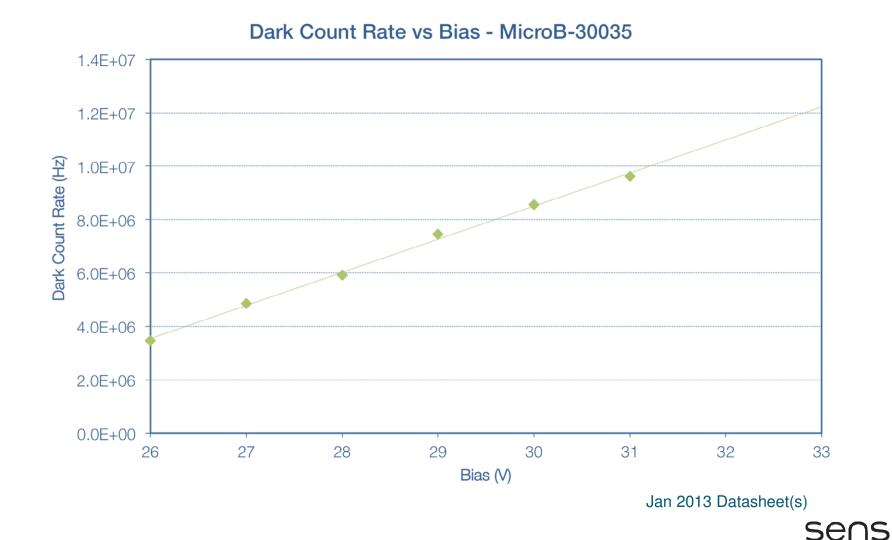
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After-pulsing vs. Overvoltage





B-Series Dark Count Rate vs. Bias

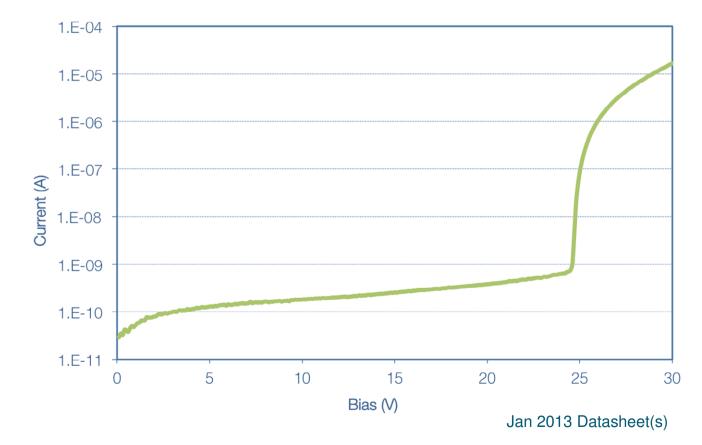


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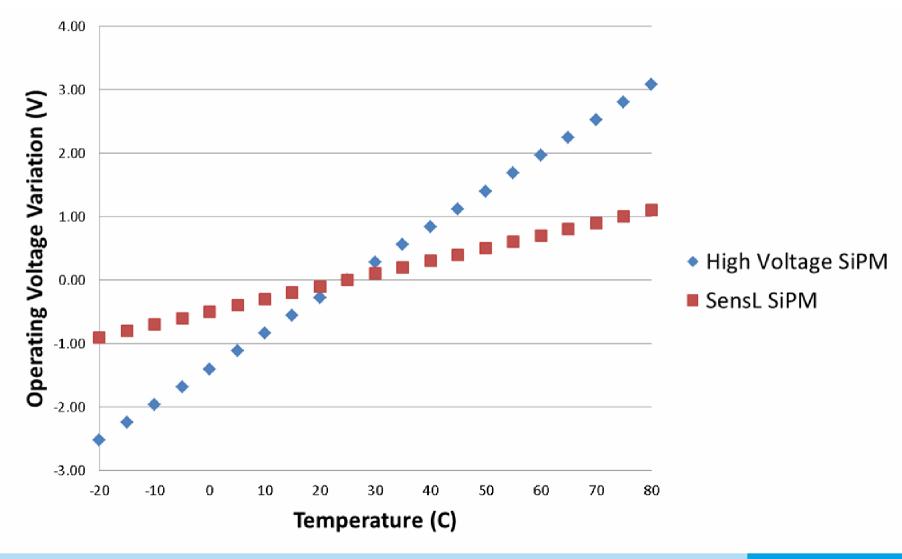
B-Series Current vs. Bias

Current vs Bias - MicroB-30035

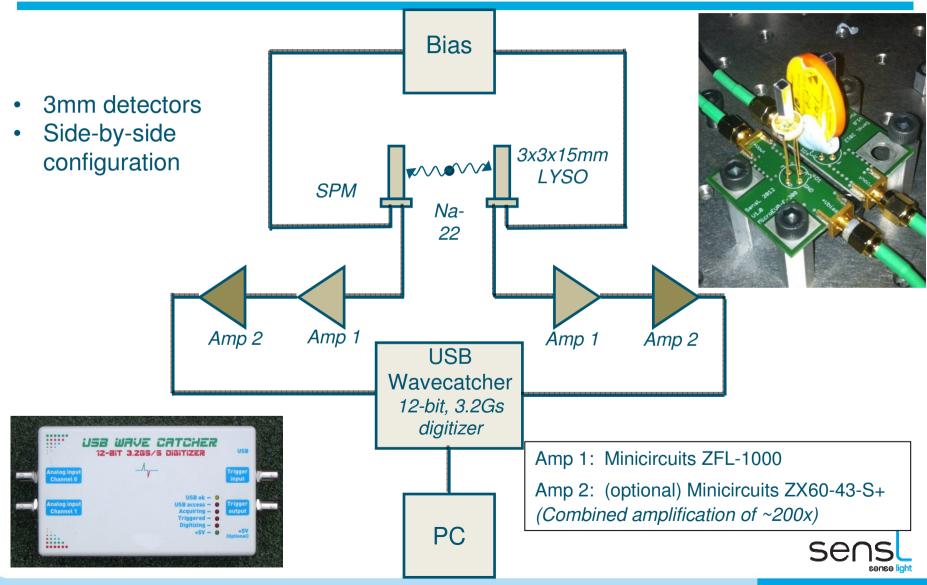




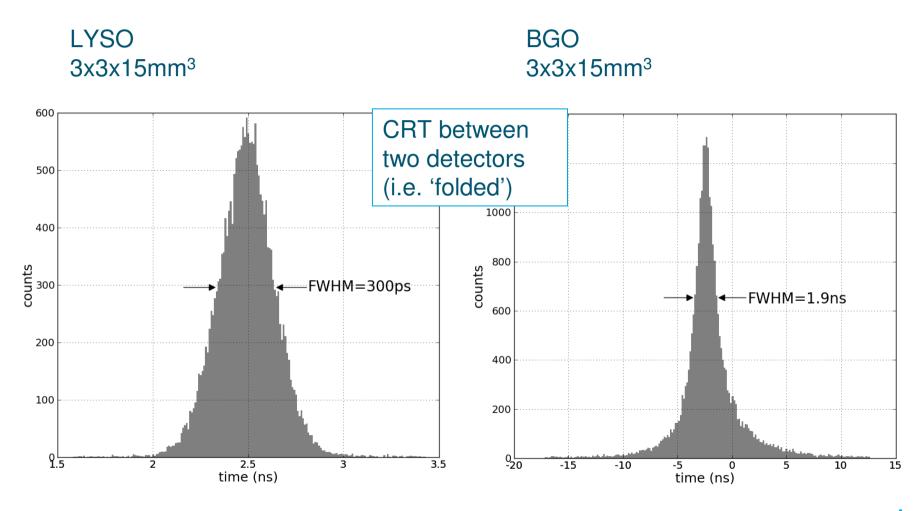
Low Temp. Dependence of Operating Voltage



Coincidence Resolving Time Measurement

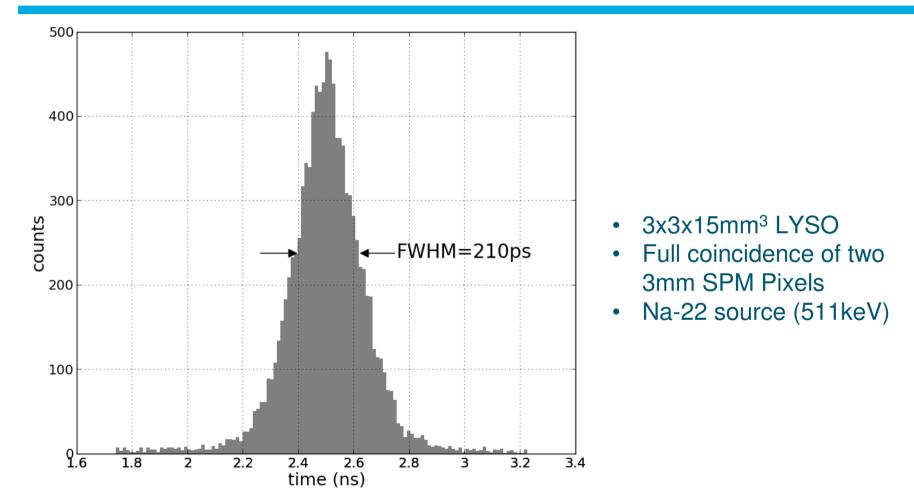


Coincidence Timing Resolution with FM



SEAS

FB - Coincidence Resolving Time 3mm Pixel Fast Output



Additional publications are available on our website at <u>www.sensl.com</u>



Sensor Capacitance

		1mm	3mm	6mm
		10035	30035	60035
	Rise time Fast Output	0.3ns	0.6ns	1.0ns
	Signal pulse width Fast Output (FWHM)	0.6ns	1.5ns	3.2ns
Fast o/p	Capacitance (Fast Terminal to Cathode)	1pF	12pF	48pF
Std o/p	Capacitance (anode – cathode)	100pF	850pF	3400pF

Fast Output Provides Low Capacitance Output Capability



SiPM Reliability

- Extensive SiPM reliability tests carried out on standard packages & detectors
- All tests were made in accordance to the relevant JEDEC standards (below)

Test	Standard Reference	Required Condition	Lot size	Duration / Acceptance	Status
High Temperature Operating life	JESD22A 108	Ambient temperature = 125°C; bias>Vbr	3 lots of 77 units	1000 hours / no fail	Pass
High Temperature Operating life	JESD22A 108 higher endurance	Ambient temperature = 125°C; bias>Vbr	256 units	2000 hours / no fail	Pass
High Temperature Operating life	Product Specific	Ambient temperature = 85 ℃; bias>Vbr	1 lot of 77 units	1000 hours / no fail	Pass
Unbiased Highly Accelerated Stress JESD22-A118 110 °C, 85% R		110℃, 85%RH	3 Lots of 25 264 hrs / no fail units		Pass
Temperature Cycling JESD22-A104 -40C to 85C, 15 sec trantitime		-40C to 85C, 15 sec transition, 15 min dwell time	3 Lots of 77 500 cycles / no fail units		Pass
High Temperature Storage Test	JESD22-A103	504hrs @ 125℃	3 Lots of 25 units	504 hrs / no fail	Pass

In February 2013 SensL launched the B-Series

Announcing the B Series UV Sensitive Silicon Photomultiplier Sense light

Medical Imaging | Automotive Radiation Detection | Biophotonics

- » 4th generation SiPM technology
- » 40% PDE at 420nm
- » Ultra fast rise time and recovery
- » Exceptional gain and optical response uniformity

- » Temperature stability of <20mV per degree C</p>
- » 30V operation
- » Lower cost than PMT
- » Shipping now in volume





Products & Pricing Overview

The SensL Advantage

- » Designed for High Volume
- » Designed for Lowest Cost
- » Designed for Uniformity
- » Excellent Customer Support



Products Introduction

- Discrete package-level sensors (SiPM and Photon Counting)
- Modules (SiPM and Photon counting)
- Arrays (small and large area)
- Readout electronics
- Nuclear medicine modules (& software)
- Measurement instruments



MicroSM & MicroSB – Discrete SPM Detectors

Standard mode (not high speed) detectors



- The MicroSM & MicroSB family of detectors are available in a variety of miniature packages
- Designed to suit a wide range of applications
- 4 detector sizes available (0.25mm,1mm, 3mm and 6mm)
- Range of microcell sizes available representing different performance trade-offs
- Low power, low voltage operation
- Readout & power supply options available
- Cooled and uncooled options available
- Package styles include: TO18, X13, TO5, TO39 (cooled)

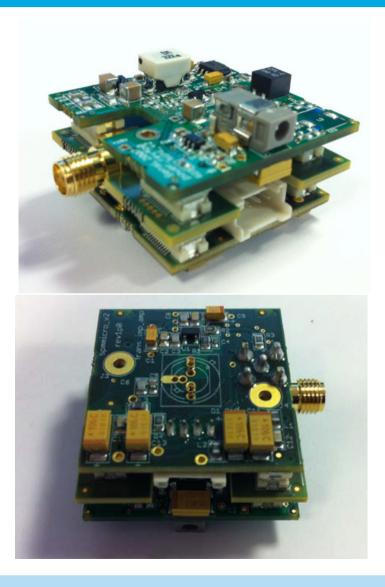
MicroSM-60035 & MicroSB-60035

Single channel 6mm pixel

- Low cost ceramic package
- Epoxy overfill 500µm
- Low voltage operation & low temperature dependency
- Electronic preamplifier boards available



Micro-EVB (standard output only)



- The Micro-EVB is designed for use with all uncooled MicroSB and MicroSM series detectors (standard output only)
- Separate versions for 1mm and 3mm detectors available (6mm detectors operate with the EVB designed for 3mm detectors)
- Based on trans-impedance circuitry
- Includes power supply and shield boards
- Low power, low voltage operation
- SMA output connector (voltage output)
- Dual power supply options



MiniSM – Cooled SPM Module



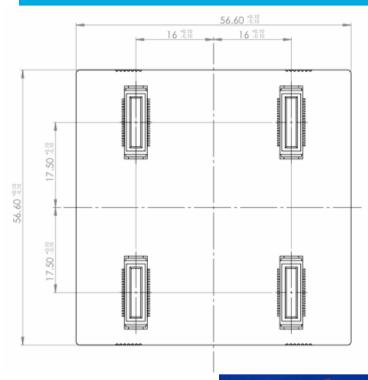
- The MiniSM is a family of detector modules that are designed as turnkey evaluation modules
- Thermoelectrically cooled (-15C)
- Designed to suit a wide range of applications, but particularly aimed at bio-photonics markets
- Two detector sizes available (1mm, 3mm)
- 35um microcells used
- Low power, low voltage operation
- Features integrated readout, cooling & power supply
- c-mount option available
- Fiber coupler option (FC) available

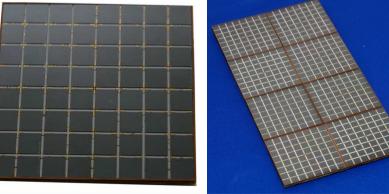




Array & Matrix Products

ArraySB-8 Large-Area 8x8 Array





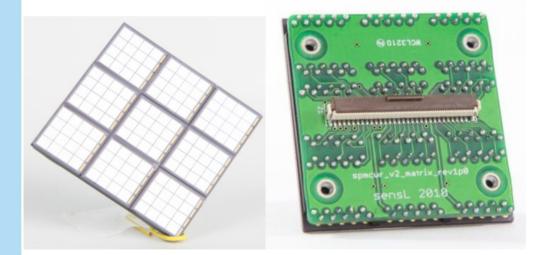
ArraySB-8

- -4-side scalable design, B-Series silicon
- •7mm pixel pitch
- •64 pixellated channels
- Single 30V power supply
- Optical Response Non-Uniformity <10%
- Replaces the H8500, R8900-C12 and H9500 position sensitive photomultiplier tubes
 - Better performance
 - Better uniformity
 - Lower cost



4x4 arrays: ArraySB-4 and ArraySB-4p9





ArraySM-4 & ArraySB-4

- 4-side scalable design
- -3.36mm pitch
- •16 pixellated channels
- Single 30V power supply
- Optical Response Non-Uniformity <10%
- Designed for simultaneous MRI compatibility

•Full system electronics available for bias control and pre-amplifier

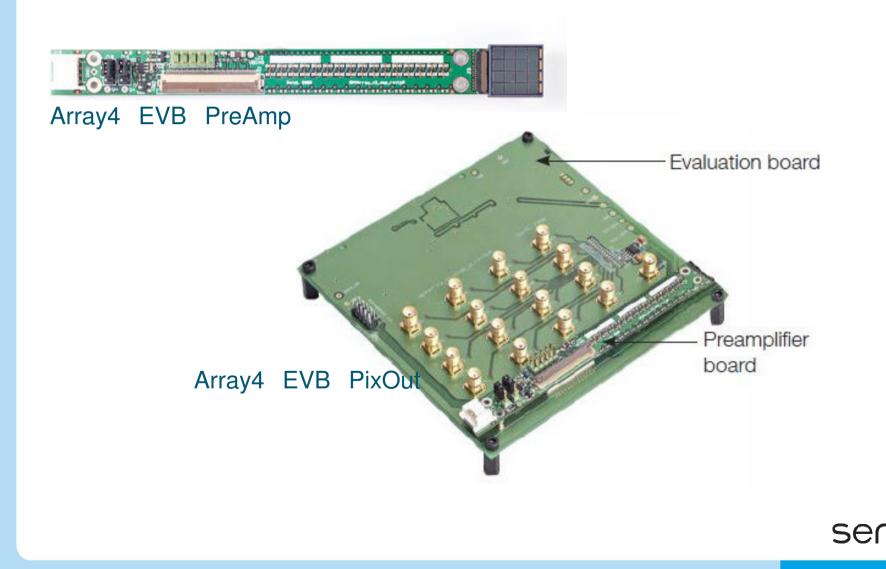
ArraySM-4P9 & ArraySB-4p9

- 4-side scalable design
- 144 channels
- -Single 30 Volt power supply
- •Optical response non-uniformity <10% (equivalent to a PMT max:min <1:1.2)

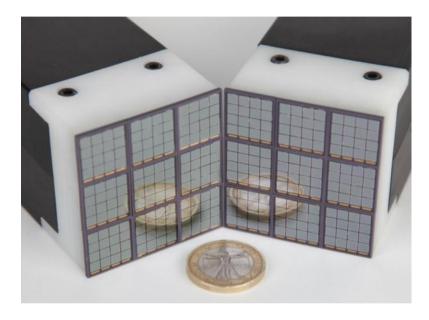
 Solid-state alternative to the H8500, R8900-C12 and H9500 position sensitive photomultiplier tubes



Array Readout Electronics



MatrixSM-9



Electronics Partnership:



A Scalable, Large Area Module for Silicon Photomultiplier Integration

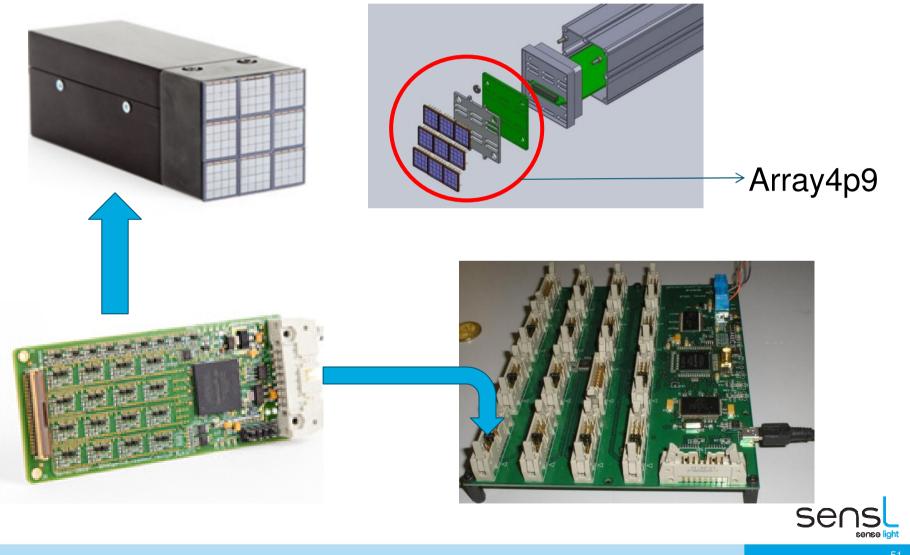
- Optimized for L(Y)SO readout
- 144 channels of 9mm² SPM
- Full digitization and coincidence processing for 2304 channels per board
- Temperature stabilization
- Available as research or OEM version
- 1x9 linear version in production
- Cable length options available



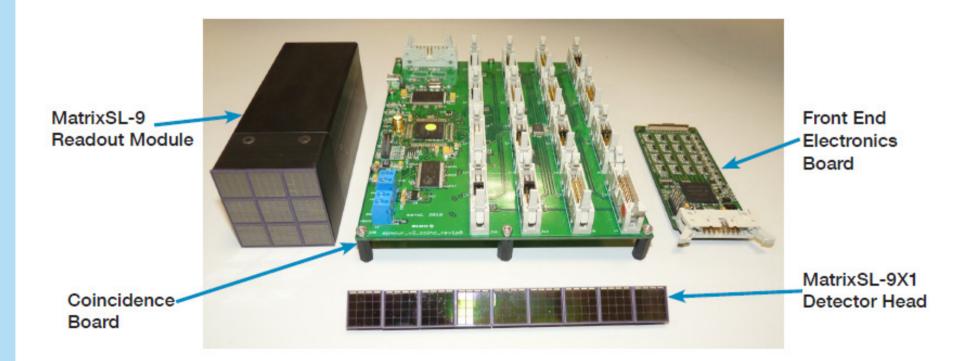
1x9 linear option



MatrixSM-9



MatrixSL-9

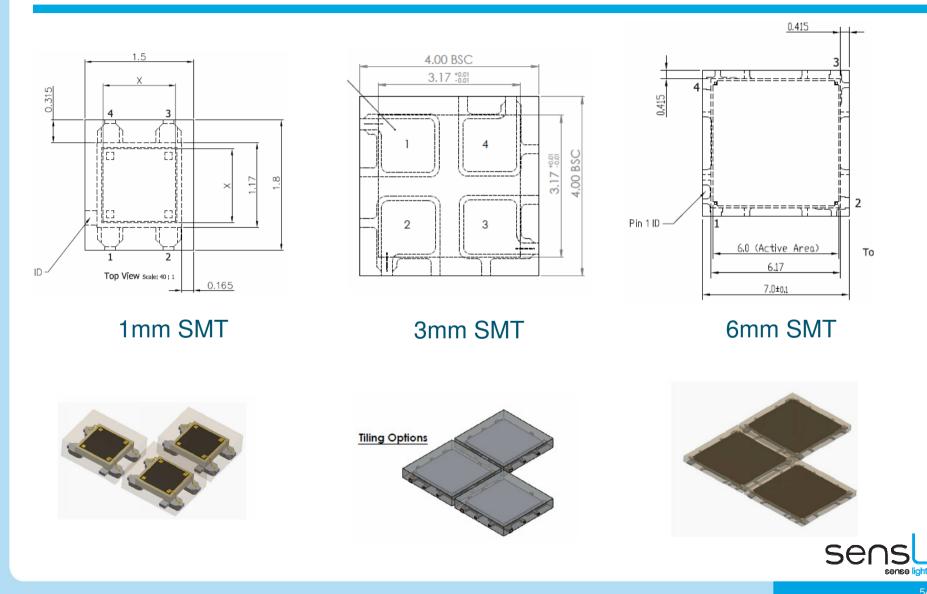






Surface Mount (SMT) Products

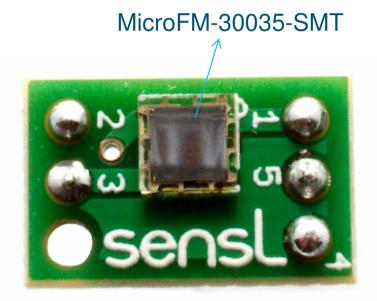
SMT Devices – Mechanical Specifications



SMT Pin-Adapter Board (SMTPA)

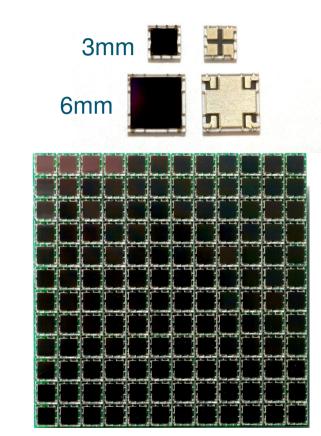
The SMTPA is a simple carrier board with pre-mounted SMT device giving users access to pins to facilitate easy testing.







.25mm, 1mm, 3mm & 6mm pixel 4 Side Tileable SMT Package



12x12 array of 3x3mm SMT parts shown. Arrays based on 6mm & 1mm SMTs are in design.

ArrayFM-30035-SMT

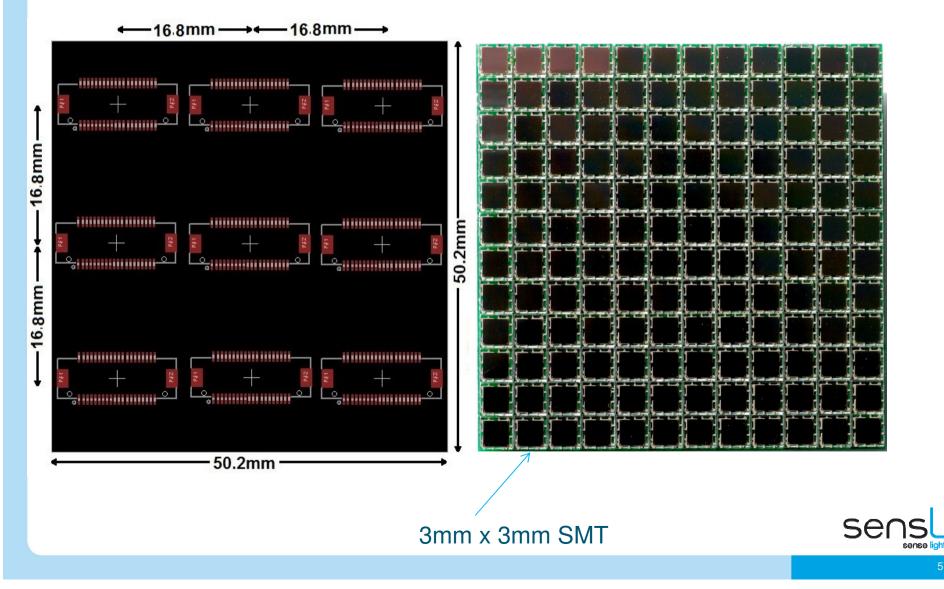
- 4 Side tileable
- <500µm from detector edge to package edge</p>
- Clear molded top surface
- Low profile 0.6mm thickness
- Close coupling capable with 200µm from SPM to top of package
- Supply Options
- -Tape and Reel (3k/reel)
- -49 unit tray for prototyping
- 3mm & 6mm Available Now
- -1mm in development

3mm SMT Application Example

- 12x12 array of 3mm SMT
- 4.2mm pitch
- 200µm flatness on standard FR4 PCB
- Provides both standard and fast readouts

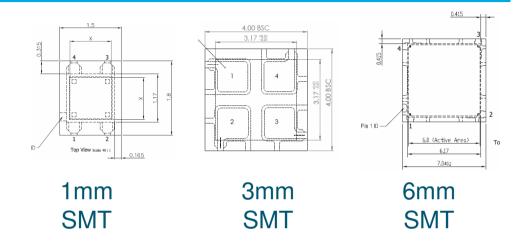


SMT Arrays – 12x12 example of 3mm SMTs



Volume SMT Shipment – Tape & Reel



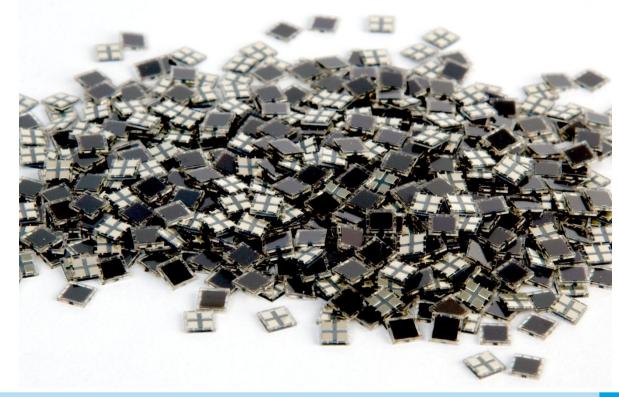


- All parts shipped as tape and reel in moisture barrier bag to J-ST 033
- **MSL=3** reflow solder compliant
- All parts ship 3000 units per tape
 - 1mm on 7" diameter (8mm width)
 - 3mm on 13" diameter (12mm width)
 - 6mm on 13" diameter (16mm width)

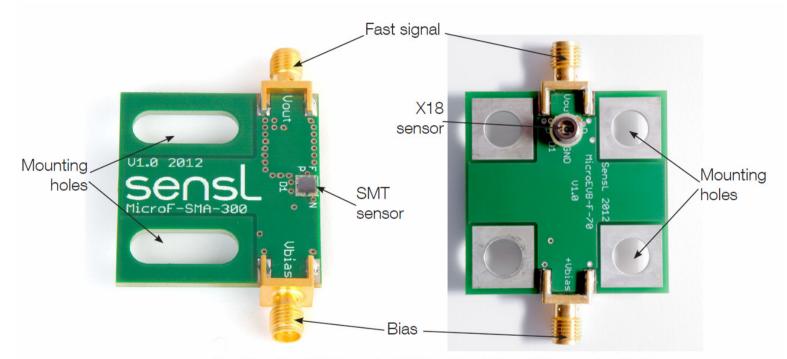


SMT detectors – High volume solution

- MSL3 compliant
- Simultaneous fast & standard readout possible
- Lead-free solder reflow compatible
- -40 to +85 Celsius operating range
- Low cost



Evaluation Boards – EVB's – for Fast SiPMs



The MicroFM-SMA boards: SMT version (left) and X18 version (right)

Fast-output detectors are available in all SMT packages and also in TO18 packaged die (1mm and 0.25mm SiPMs)

MicroFM-SMA boards are for fast mode readout of TO and SMA packaged 0.25mm, 1mm, 3mm and 6mm detectors SC



Measurement Instruments: TDC & CFD

Measurement Instruments – TDC & CFD

A detector's performance can be limited by the electronics which are used to read it and acquire the signal it produces.

SensL offers two products relevant to such applications:

HRM-TDC (Time to digital converter)

HRM-CFD (Constant fraction discriminator)





HRM-TDC



- Portable, highly functional timing system
- Flexible, easy-to-use timing functions
- Four channels, each with 27ps timing resolution
- Maximum data rate of 4.5MHz over USB Programmable TTL clock output
- Directly compatible with PCDMini & HRM-CFD
- User GUI, DLL's & Lab VIEW examples provided
- OEM versions available (with MOQ)



HRM-CFD





- Portable 2-channel CFD system
- Picosecond timing with ultra-fast detectors, low time walk/jitter
- Compact, rugged and low-power
- 0.75GHz amplifier per channel
- All settings programmed via USB & GUI
- Fully compatible with the SensL HRM-TDC
- Compatible with PMT, APD, MCP, PIN & SPM style detectors
- OEM versions available



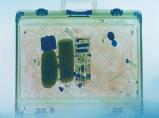


Markets & Application Areas

Large Diversified Markets and Applications



Medical Imaging PET/CT, PET/MR, SPECT, Gamma Camera



PM1 and pin diode replacement combining high performance with small form factor and low cost for use in hazard and radiation detection from large area cargo screening to handheld isotope detection and identification systems

Hazard and Threat Detection

Radiation Detection, Cargo Scanning



3D imaging, range finders, aerial surveying, robotics, and transportation silicon photomultipliers detection solution for improving accuracy and lowering cost for high volume range finding applications

Automotive and Industrial

Advanced Driver Assistance, Laser Range Finding, Robotic Automation, Nucleonics, Process Inspection



Silicon photomultipliers for high throughput and point of care systems for law yotners, tood markis, bounging, fourescorce detection, spectroscopy applications and portable diagnostic sequement

Biophotonics

Hematology, Flow Cytometry, DNA Analysis, Flouresence, Spectroscopy



Academic Research & Other Applications

Biophotonics (not covered in this presentation)

- ATP monitoring
- Flouresence analysis
- Cytometry
- Flouresence lifetime imaging (FLIM)
- Time correlated single photon counting (TCSPC)
- Confocal Microscopy
- Retinal scanning
- Blood analysis
- Data communications
- Space-related programs (ESA, civilian satellites, LiDAR)
- High-energy physics programs ongoing (CERN, DESY, GSI, PSI, LANL, INFN...)
- Cherenkov radiation detection (CTA)
- Turbine temperature monitoring
- Multiple photon counting applications (particle sizing, scientific...)
- Dark matter experiments



Recent Academic Papers on our Website <u>www.sensl.com</u>

- Stanford
 - Fast Readout
- UC Davis
 - Matrix 9
- U Manitoba
 - HDMI Cable
- GE/SensL
 - Fast Readout
- McGill University
 - Highly Pixelated Readout

				Evaluation of Matrix9 for Small-Animal PET Junnei Du', Jeffey Schmäf, Yongleng Yang', Kun Dr', Emile Roncali', Nikolai Parkor ² , Steve Buckley ² , Carl Jackson ² and Simon R. Cherry ¹				
				¹ Department of Biomedical Engineering, University of California, Davis "Senst, Technologies Ltd., 6800 Airport Business Park, Cork, Ireland				
Timing Performance of F Silicon Photomulti		head controls of a 3 - 3 month of DFM arrays, such with C + 2 1. 1 = 3.1 month of DFM arrays, such with C + 2 1. 1 = 3.1 month of Terminal Control of Terminal Control of Terminal of the 144 detection basis using just 25 detections; channels of the 5 stopy was to added by performance of the Matrixi		silicon photomultiplier (SPM) adout electronics. The detector is, each with 4 × 4 pixel/V. The and each SPM pixel measures adout technique is used to read tronic channels ¹⁷ . The purpose e of the Matrixi detector when sheet with small-arimal PET	C and a second s	Figure 3 Bustrates the mergy resolution obtained at offerent bias voltages bias voltages. the detector is solved and seguratures. At higher bias voltage, the detector is solved and the second second attractional second second second second second attractional second second second second attractional second second second second second second attractional second second second second second second second second attractional second		
Jung-Yeol Yeom ¹ , <u>Ruud</u> Vinke ¹ , Nikolai Pavlov ² O'Neill ² , Carl Jackson ² and Craig	To find the best wo ratio (SNR) ⁽²⁾ , ener measured and com 25 °C, in 5 °C inter	Pane 0	the noise, signal, signal-to-noise yram and timing resolution were peratures, ranging from 5 °C to measurements were obtained at	methods: M1) all energies me method. M3) region of interest method. The 'ROI method' uses surrounding pixels. "Offset call subtracted from the signal (if it FWHM of the noise distribution 5 (iet) shows the flood histog histoream runkin using the fin	I posicion vada calculateo langi toto "atteretti hoof", (KC) al vergeise with offast calibration (ROI) vertuod", (M) ROI with offast calibration ROI) vertuod", (M) ROI with offast calibration terratori meenin tatte signal atteretti versi fratt se utilitated signal was stratiler than half the substrated signal was stratiler than half the substrated signal was stratiler toto in Figure and figure 5 (right toto) whom the flood to ratehousis, Inger 5 (right toto) whom these TROI with offset calibration method. The flood stratistics in the flood histogram/R. A smaller am quality.			
Molecular Imaging Program at Stanford, Dept. of Radiol and Electrical Eng. ⁵ , Stanford University, Stan SensL Technologies Ltd., 6800 Airport Busines	M	The state of the s						
MIPS Program at Stanford	Stanford University School of Medicine Department of Radiology	coupled to the cent other eight SPM a source, placed 20 the crystals excep resolution measure	d LSO arrays (pdm 15 m were used for all measu er of one SPM array via li tays were covered by bla m above the font of the t the timing resolution merits, the source was lo detectors with a center-to- Results	IC-830 optical grease, whilst the ick paper. A 100 µCi mGe point ISO array was used to imaliate measurements. For the timing cated at the center of two LSO center distance of 80 mm.	were (29.7+0.02*T) V. The red, the raw data (leading edge dis and "LED time walk and crystal and dashed curves in foure 5	pectra and timing resolution. The bias voltages blue and green curves indicate the results from crimination (LED), "LED time walk calibration" timing shift calibration", respectively ⁴⁷ . The solid (initit) indicate the timing resolution for each		
PROCEEDINGS OF SCIENCE	_	to the cost of the		Figure 2 shows the signal, noise and SNR at different bias voltages and tempora- tures. The signal is the amplitude of the photopeak potions. This signal ampli- tude was corrected by subtracting the channel of the noise distribution of the the pixels was treated as the detainter once and the	nesocited.	y window and a 400-000 keV energy window		
SensL New Fast Timing Silicon Photomultiplier	2012 IEEE Nuclear Science Symposium and Medical Imaging Evaluation of Very Hi	ghly Pixellated Crysta		the detector noise and the SNR was the ratio of the 511 keV photons amplitude to the detector noise/ii. The "best SNR was obtained at a bias voltage of 30.0 V except at 25 °C, where the optimum occurred at 30.5 V.	Discussion The best working bias voltag histograms show that LSO array and indicates that smaller crysta timing resolution of 37 ns can these attractive features, high	n and Future Work to Marii@ is around 30.0 V. The food s with a plath of 1.5 mm can be deady resolved is (-1 mm plath or smaller) might be resolved. As be achieved with proper time calibration. With -vestulation smaller) might and PETIME is for breast and brain imaging, could be based		
Kovin O'Neill' Sent Technologies Limited 6000. Super Tautous Park, Cork, Ireland E-mail: Score 11 Score 11. com	Blocks with SiPM Rea PET/MR Detectors in a Christopher J. Thompson, Senier Member JEEE, Andre	Small Animal PET Ins	ert _	breakdown voltage goes up with increasing temperature (~20 mW*C).	upon these large-area detectors References [1] Mathits system user manual, t [2] Y. Yang et al., Phys. Med. Biol. [3] Y. Wu et al., Phys. Med. Biol.			
Nikolai Pavlov Seni: Teohnologia: Luniat 0000 Apport Buinca: Park Cork, Iseland E-mail: uportor@sono1.com	Retière, Greg Stortz, Vesna	I Sossi, and Xuezhu Zhang I. britonecritos Our group are potently studying the fr construction a small animal PET scenarer which	asibility of 70		DAVIS OF CALIFORNIA	cmg		
Serged Delinsky Gřipálen (zmerk) Emel diskundyzberech (pr. cm Cri Jackson Ser, Zeolonjou Lando dil Algor Hance Jele A Jakon dil Algori Hance Jele A Jakon	¹ Advance. ¹ The second second process and process multiplets to 1971 MM inters to a make the physical second second second second second second methods process and the second second second second second methods and the second second second second second second and the second second second second second second second methods and the second second second second second second methods and the second second second second second second methods and the second second second second second second beyon and the second second second second second second second beyon and the second second second second second second second beyon second second second second second second second second beyon second second second second second second second second second beyon second second second second second second second second second beyon second secon	$v_{\rm est}$ is static difference of the probability of the probabilit		Applic Compatib	<section-header><section-header><section-header><section-header><text></text></section-header></section-header></section-header></section-header>			
In this paper we raper at a part of any field-setting (2017), are indecised with Additional riginal raper. This is abbattomic of the two rep for angle physics descense sequence $1 \le i \le$ FWDD. This near derives can be availy singured and the physics with an additional for the spectra is a second 250 study and any star of the spectra physics of the star SM for a lower Δn sequence with typical 2-bots for SM for a sole star of the spectra Resolution in the spectra physics of the star of the spectra physics of the star Resolution in the spectra physics of the spectra physics of the star of the spectra Resolution in the spectra physics of the spectra physics of the star of the spectra Resolution in the spectra physics of the spectra physics of the star of the spectra physics of abatta physics of the spectra physics of the star of the sphysics of the star of the star of t	for cory and in the order have based over early identified with a park, it will be present of the order of the order of the order park is will be present of the order of the order of the order and the order present in the data large array suggesting the the intergraph second in the data large array suggesting the the intergraph second in the data large array suggesting the intergraph second in the data large array suggesting the intergraph second in the data large array suggesting the data second array or a suggesting the data second array of alternative array of the data second array of the data array of the second array of the data second array of the array of the data second array of the data second array of alternative array of the data second array of the data array of the data second array of the data second array of the data second array of the data second array of the array of the data second array of the data second array of the data second array of the data second array of the data second array of the data second array of the data array of the data second array of the data second array of the data second array of the data second array of the data second array of the data second array of the data second array of the data second array of the data second array of the data second array of the data second array of the data second array of the data second array of the data second array of the data second array of the data second array of the data second array of the d			Andres C. Goo Chen Yi Lin Guo Yi Lin Guo Yi Lin Guo Yi Lin Hang Chen Chen Chen Chen Hang Chen Chen Chen Hang Chen Chen Chen Hang Chen Chen Chen Karlow (2010) Andreas a best seguing prove for a 10 ⁴ M hand FTI for Index of the State of the Index of the State of the Index of the State of the Index of the State of the				
the paper well associated that provides phases for photon event provides significantly theorem (27), sequencing to the pTOE supervision. Section 2019, Section 2019, Photon detectors, Left Oracle, Paperland, and Paperland, Section 2019, Section 2019, June 15-15, 2017	¹ Manuscript data framming (1012). This was is no metric of the second second second second second second of Carabita (Cold Second Sec	plasmed to have up to its such resp. I. MATURALE AND METHODS A. Description of Coysial Arrays The crystal arrays parchased from P according to the fibroing postfloations: IOPER LATER: Marrial: LTDD: Ce Marrie: Add elements Size: 1.2d.1.3 meV, Pack: 1.370 mer Theistense: Over all Apoptoris: II.16.6 at 16 me ⁻²	Jahanda bawe up to six waké renge. H. RUTERALE KON MERIODE A. Divergine of Coynel & event The crystal arrays particulated from Posteue Inc. according to the Bibewing specifications: Houring LTSD: C. Marcet: Ad classes Marcetal LTSD: C. Marcet: Ad classes Marcetal LTSD: C. Marcet: Ad classes Marcetal LTSD: C. Marcet: Ad classes		<text><text><text><text><text><section-header><text></text></section-header></text></text></text></text></text>			
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Select Medical Imaging Design Wins

Commercial Customers

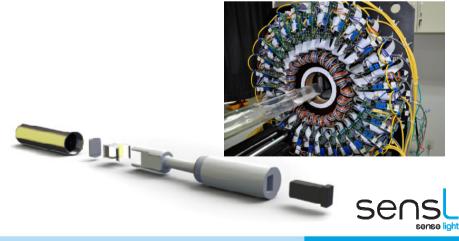
Brain PET/CT System (US)

- FDA Trials now @ 2 hospitals
- First commercial system results
 Published SNM-June-2012
- •Full Body PET/CT System (US)
 - Active development
- -Small Animal PET (Asia)
 - Field Trials

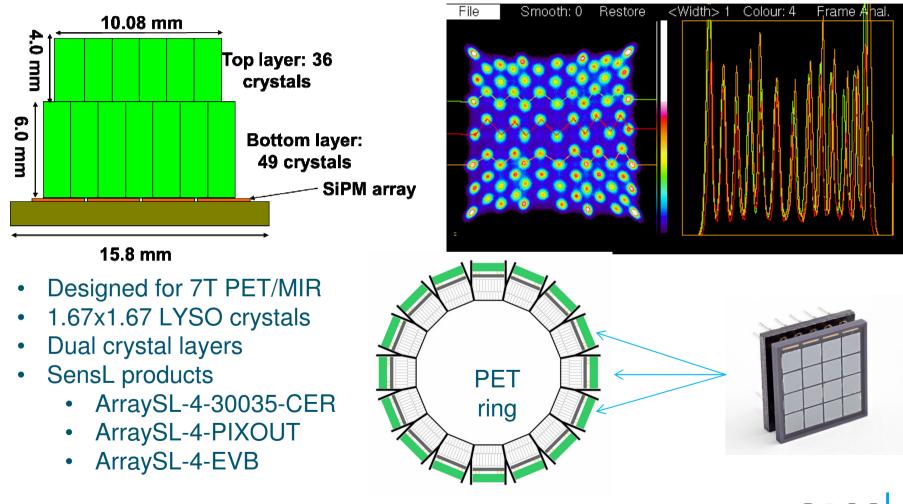


Research Customers

- Brain PET/MRI Scanner (Samsung Research)
- Brain PET/MRI (Stanford)
- Prostate Probe (WVU)
- High Resolution Breast PET (MD Anderson)
- Preclinical PET (Large Chinese University)
- 80 Research papers available on SensL website



High Density LYSO Crystal Block Readout

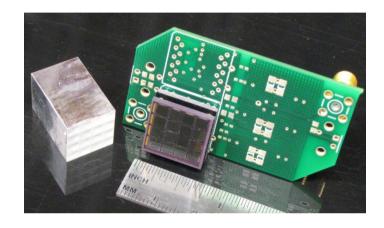


* Images courtesy of Chris Thompson



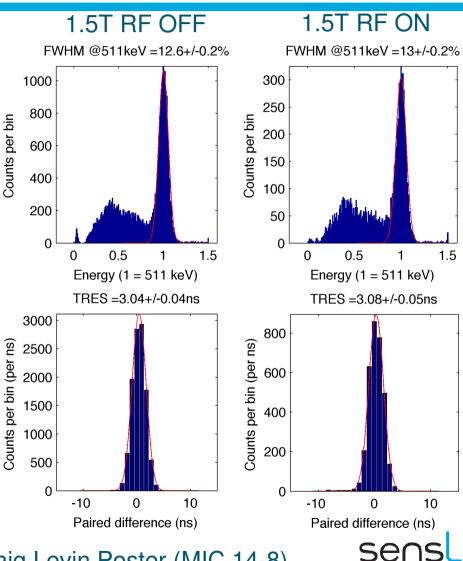
PET/MRI Molecular Imaging Program at Stanford

Counts per bin



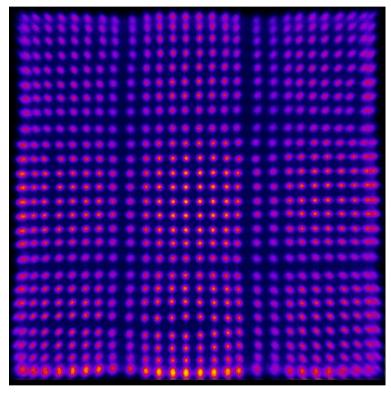
PET/MRI Readout through SPM modulated VCSEL over fibre •2.14x2.14x20mm³ LYSO •All components selected for magnetic field compatibility

* Images courtesy of Peter Olcott and Craig Levin Poster (MIC 14-8)



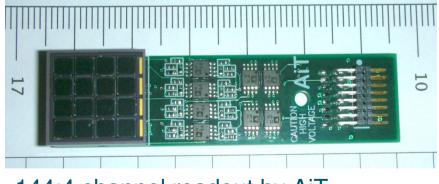
sense <mark>lic</mark>h

PET - High Density Signal Multiplexing West Virginia – Center for Advanced Imaging



A 1.5mm LYSO Array flood map DOI and MR compatibility Multiplexing from 144:4 channels

SensL Array4p9

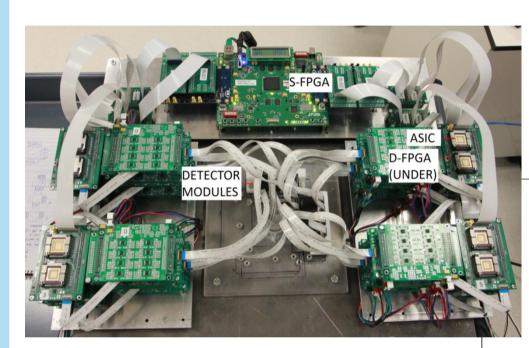


144:4 channel readout by AiT

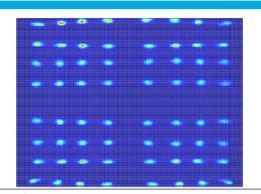


* Images courtesy of Stan Majewski

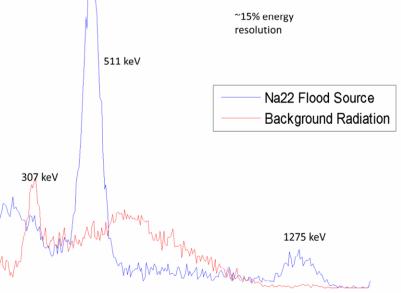
High Resolution PET System MD Anderson



Custom ASIC readout 2mm pitch, 30mm length LYSO array 2ns timing 14% energy resolution 3-4 Depth of Interaction



Single Pixel Energy Spectrum

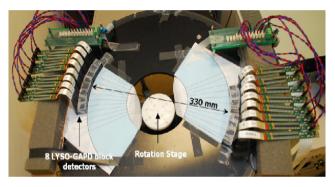


* Images courtesy of Chad Birchner and Yiping Shao

Ser

SensL Multi-Modality Nuclear Medical Imaging





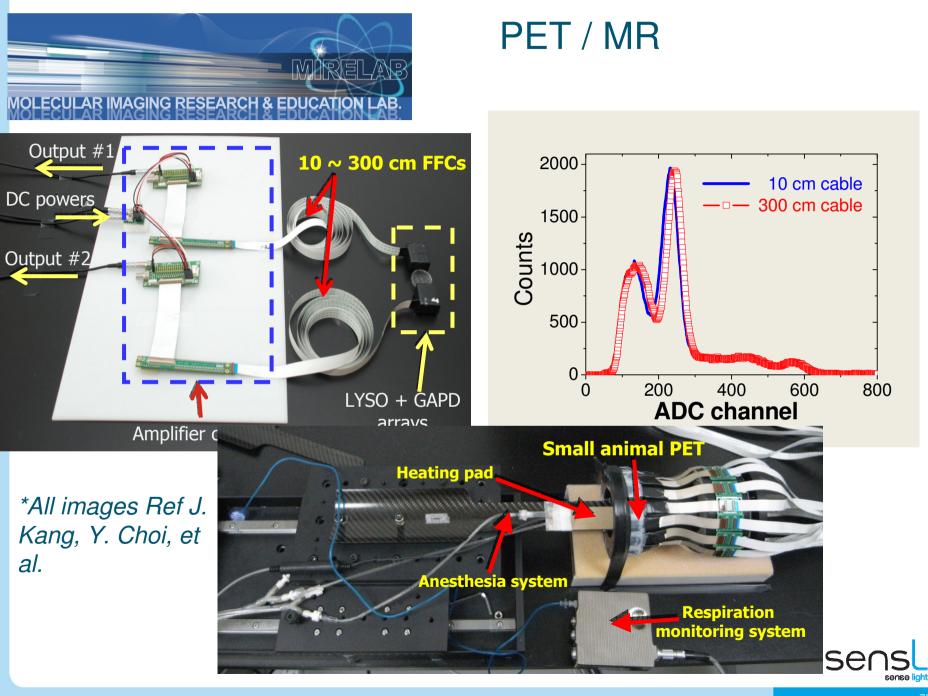
World's first PET/MRI Ring





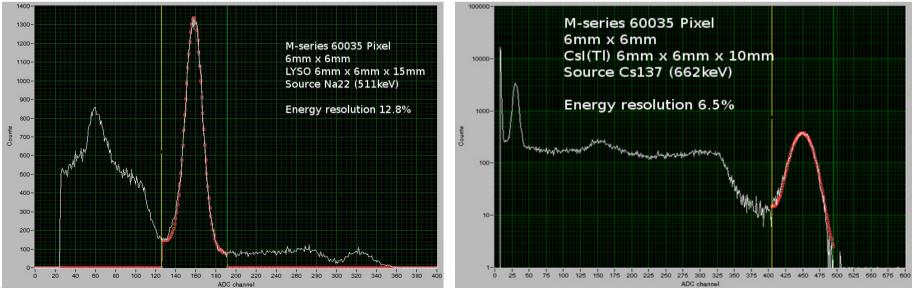




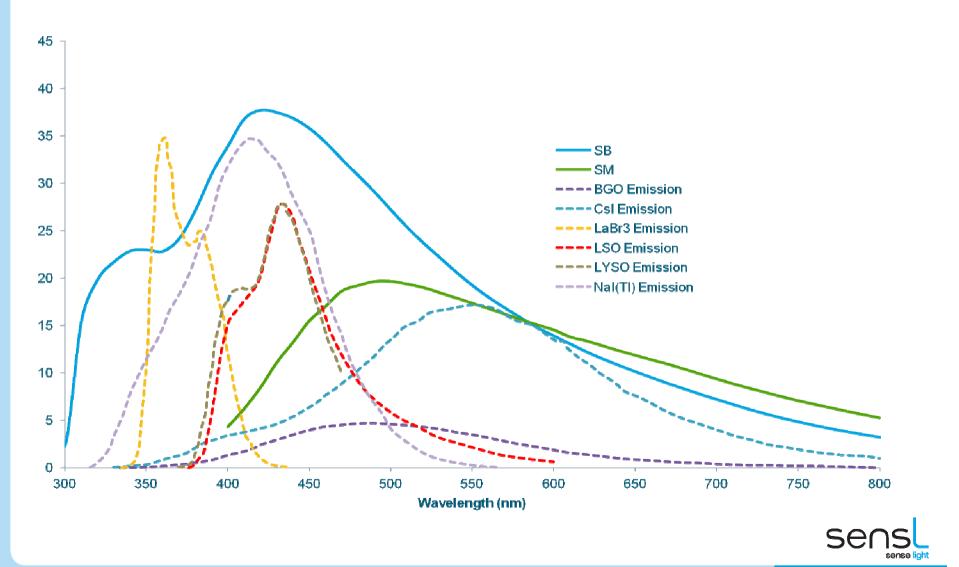


Nuclear Detection / Spectroscopy

- SensL detectors have need designed into numerous radiation detection systems:
 - Handheld dosimeters & counters
 - Large portal/truck scanning systems (neutron & gamma)
 - Handheld spectroscopy (isotope identification) systems
 - Customers are currently investigating SiPM-based neutron detection
 - Hazardous waste storage monitoring
 - Industrial scrap metal sorting
 - Nucleonic level measurement



Common Scintillators & SensL SiPMs



LIDAR Requirements

- LIDAR Requirements
 - Wide detection range
 - High range accuracy
 - Temperature stability
 - Miniaturized
 - Rugged
 - Low power
 - Low cost
 - High Speed

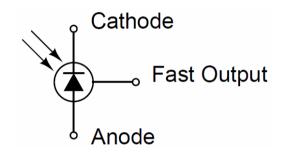
- SensL SiPM Benefits
 - Dynamic range
 - -Ambient light rejection
 - -Temperature stability
- Benefits of SiPM Technology
 - -High signal to noise
 - -High gain
 - -High uniformity
 - -Multi-sensor capable
 - -Low power
 - -Low cost

SiPM sensors are a superior alternative to the APD and PIN Photodiode



Example - SensL SiPM for Automotive LIDAR

- Advantages of SiPM over PIN or APD
 - Gain of SiPM is >1M
 - Output response is picoseconds
 - Temperature stability
 - Uniformity of output response
 - Wide dynamic range
 - Large area array compatible
 - CMOS compatible
- Advantages of SensL SiPM for Automotive
 - Patented Fast Output terminal provides extremely fast output response
 - Picosecond response times provide the highest range accuracy possible

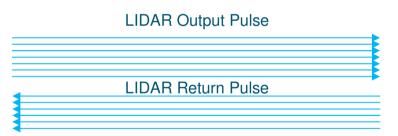


Circuit Designator



SiPM Dynamic Range & Automotive LiDAR?

- Reflected light intensity varies by orders of dynamic range
- SensL SiPM provides wide dynamic range accuracy
- Benefits of a wide dynamic range sensor
 - Ability to sense high photon flux signals
 - Ability to sense low photon flux signals









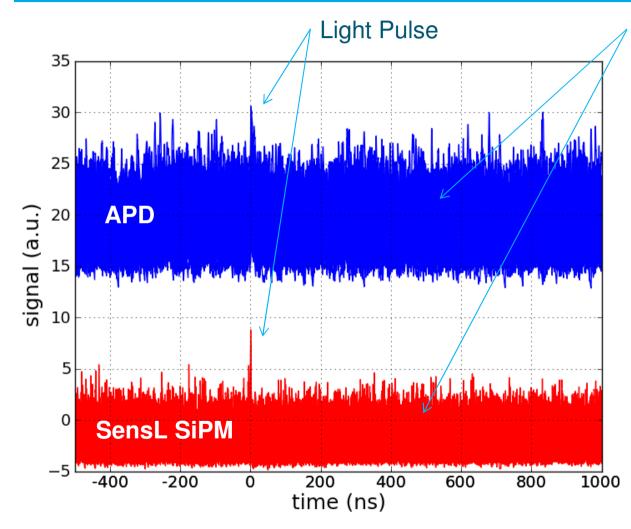


Ambient Light Rejection in Automotive LiDAR

- Automotive LIDAR systems must deal with reflected ambient light from the environment
 - Sunlight
 - Environmental lighting
- Ambient light can be rejected through system design
 - Reduction in field of view
 - Filters
 - Sensor with better ambient light rejection
- Benefits of ambient light rejection at the Sensor
 - Improved range accuracy
 - Wider dynamic range
 - Reduced system cost



Ambient Light Rejection Example



Ambient Noise

- This is an example of a low photon LIDAR signal pulse in a high ambient background
- Amplifier noise
 excluded
- SiPM provides superior background suppression



SiPM Temperature Stability & Automotive LiDAR

- Temperature stability is required to maximise range accuracy over the operating temperature range
- Benefits of a temperature insensitive sensor
 - Minimal need to adjust bias voltage with temperature
 - No need for a variable gain amplifier
 - Reduction in calibration requirements
 - Increased system stability over operating lifetime
 - Ability to have multi-sensor or arrays for Imaging LIDAR

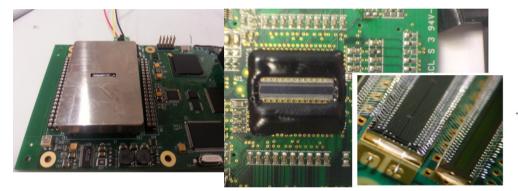
	APD	SiPM
Operating Voltage Variation	50V	0.5V
Temperature Stability	0.65V/°C	0.02V/°C



Advanced Imaging LIDAR

LIDAR ranging and Imaging System for MARS Lander

256x1 linear array with a dual ASIC packaged with TEC controller and interface board.



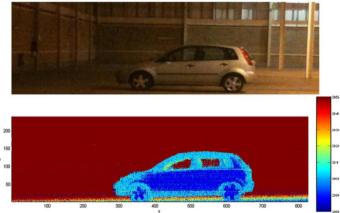


Image taken using SensL's detector head for ESA Imaging LIDAR program

Detector head and interface electronics provides high resolution LIDAR ranging and imaging.

20Km accurate to +/- 1.5m for ranging

5Km accurate to +/- 1.5cm for imaging

•Coarse ranging clock = 100MHz.High resolution red•Return Time = Count x 10 x 10^{-9} High resolution useDistance = $0.5 \times$ Return Time x 3×10^8 Interpolator accuracy is +/-50ps•Distance = $1.5 \times$ Count MetresImaging accuracy•Accuracy is +/- 0.75 metresImaging accuracy

High resolution required over < 5Km High resolution uses interpolators for sub 10ns resolution accuracy is +/-50ps

Imaging accuracy = $3 \times 10^8 \times 50 \times 10^{-12} = +/- 1.5$ cm

See http://www.esa.int/Our_Activities/Technology/Laser_radar_illuminates_the_way_to_deep_space





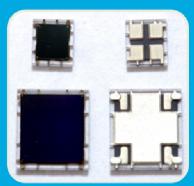
Quality Assurance & Testing

Product Level Test Plan



Wafer Level Test (at foundry)

- Process Control Monitor PCM (5 site)
- Product (all die)
 - Electrical test below and above breakdown voltage
 - Optical test (blue light) below and above breakdown voltage
 - All parts binned and failing parts removed from supply chain



SMT Product Test (at vendor)

- Visual Inspection (all die)
- Electrical end of line test (all die)
- Failing parts are removed from supply chain and destroyed
- All passing parts are supplied on tape and reel



Wafer Level Product Test

PROBE OPERATION	TEST NUMBER	TEST DESCRIPTION	Units
P1 (DARK)	01025	OPEN TEST (PROBE QUALITY CHECK)	nA
P1 (DARK)	01035	SPM OPEN_SHORT TEST (DIE CHECK)	V
P1 (DARK)	01085	BREAKDOWN VOLTAGE VBR SPM	V
P1 (DARK)	01105	DARK CURRENT AT 26V REVERSE BIAS	nA
P1 (DARK)	01115	DARK CURRENT AT 27V REVERSE BIAS	nA
P1 (DARK)	01125	DARK CURRENT AT 28V REVERSE BIAS	nA
P1 (DARK)	01135	DARK CURRENT AT 29V REVERSE BIAS	uA
P1 (DARK)	01145	DARK CURRENT AT 30V REVERSE BIAS	uA
P2 (LIGHT)	01535	SPM OPEN_SHORT TEST (DIE CHECK)	nA
P2 (LIGHT)	01615	CURRENT AT 27V REVERSE BIAS	uA
P2 (LIGHT)	01625	CURRENT AT 28V REVERSE BIAS	uA
P2 (LIGHT)	01635	CURRENT AT 29V REVERSE BIAS	uA
P2 (LIGHT)	01645	CURRENT AT 30V REVERSE BIAS	uA

- Industry standard wafer level image sensor test equipment with custom SensL probe card
- Automatic batch processing of 25 wafers at a time
- Test conditions
 - In Dark electrical tests
 - In Light optical tests using filtered blue illumination
 - Tests temperature controlled to 25°C
- Parts are binned to SensL specification with failing parts electronically "inked"
- Data files are shipped encrypted via FTP for processing and storage at SensL



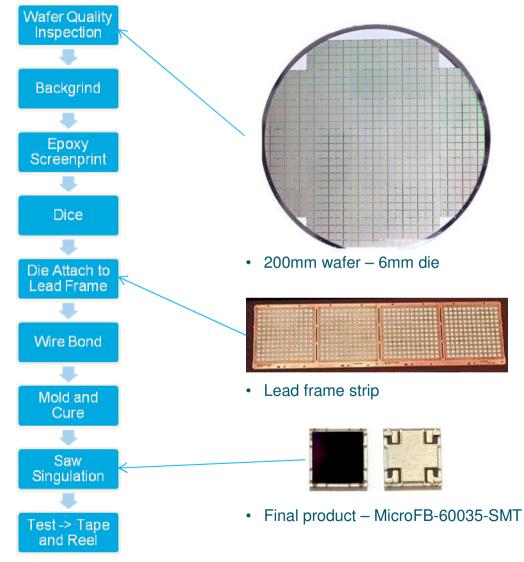
Image Sensor Tester



Temperature Controlled Wafer Chuck



Surface Mount Package Assembly Process



- All parts tested to SensL specification
- Data verified against wafer level data at the batch level
- 3000 parts per tape and reel (1mm, 3mm & 6mm)
- MSL=3 status achieved for reflow solder and mass production of arrays



SMT Devices -- End of Line Test

Test Name	Unit	Electrical Test Conditions		
		Apply forward bias @ 1V		
Open Check	mA	Measure Current		
		Test in dark		
		Apply 26.00V		
I_DRK_26V	nA	Measure current		
		Test in dark		
		Force 100nA		
VBR_100NA	V	Measure voltage		
		Test in dark		
I_DRK_VBR_1V	μA	Apply Voltage of V1 = (VBR_100NA + 1.00V) Measure current		
		Test in dark		
	μΑ	Apply Voltage of V2 = (VBR_100NA + 2.00V)		
I_DRK_VBR_2V		Measure current		
		Test in dark		
	μΑ	Apply 30.00V		
I_DRK_30V		Measure current		
		Test in dark		
F_Test_Vrms	mV	Apply 100kHz, 10.0V peak to peak sinusoidal signal across PN terminals. Measure the output RMS voltage at the F terminal.		

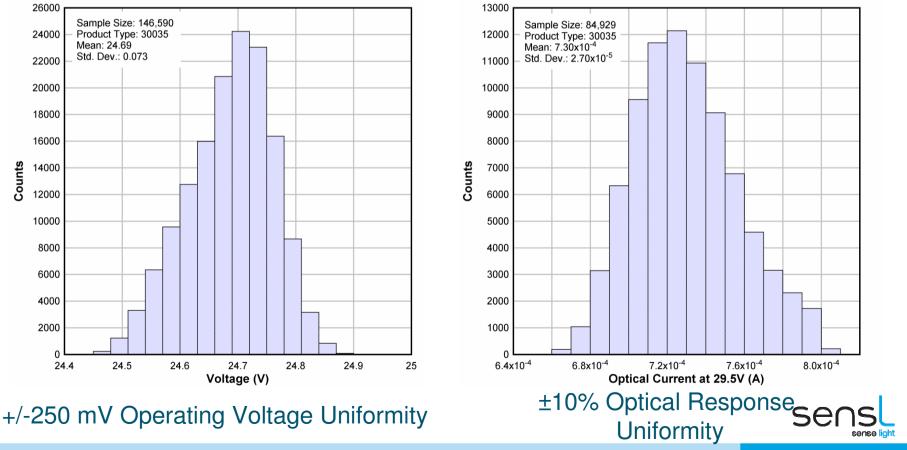


- Standard test handler modified to satisfy SensL test specifications
- All parts tested electrically
- All parts optically inspected prior to tape and reel



Electrical and Optical Uniformity

- With high volume CMOS processing capabilities, SensL has the best uniformity in the industry.
- Data is from >150k 3x3mm Pixels (un-binned data)





design detect today

The Leaders in Silicon Photomultipliers Since 2004

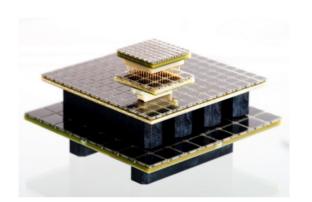
SensL – New Developments in Silicon Photomultipliers

April 2014



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SensL SiPM Product Portfolio



Arrays

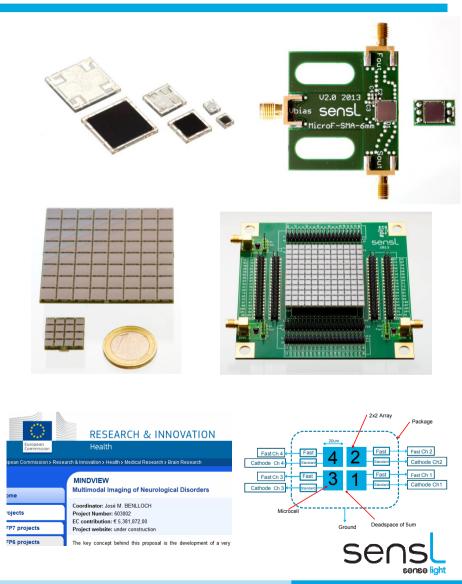


PET Readout Matrix



Recent Product Introductions & Contracts

- B Series Released for Production
 - Version 2.0 of Datasheet Available
- SMT Devices & Test Boards
 - .25mm & 1mm (M Series)
 - 3mm & 6mm (M & B Series)
- SMT Arrays & Test Boards
 - 4x4 of MicroFB-30035-SMT
 - 12x12 of MicroFB-30035-SMT
 - 8x8 of MicroFB-60035-SMT
- Photon Counting Arrays
 - 2 x 2 microcell 20u Array
 - 20u single cell sensor
- Program Partner in FP-7 "Mindview"
 - Brain PET Imager



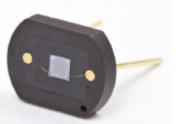
B Series Performance Overview

B-Series Summary Performance Parameters (See Datasheet for full details)

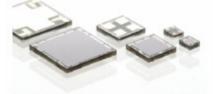
		10000 series		000 ries	60000 series	
		10035 🕫	30035 여	30050 a)	60035 ^{d)}	
Typical breakdown voltage (VBr) 🕸		24.5V ± 0.5V				
Bias range (above VBr)		1V - 5V				
Spectral range		300nm - 800nm				
Peak wavelength (λ_p)		420nm				
PDE at $\lambda_{\rm p}$	@ VBr +2.5V *)	31%	31%	35% ø	31%	
	@ VBr +5V	41%	41%	47%	41%	
Gain ^{a) e)}		3x10 ⁶	3x10 ⁶	6×10 ⁶	3x10 ⁶	
Dark current - Typical *		0.3μΑ	3.2µA	7.2µA	10μΑ	
Dark current - Max. «)		0.6μΑ	6.0µA	13.5µA	24μΑ	
Rise Time (Fast Output) a) \$		<0.3ns	0.6ns		1ns	
Signal pulse width - Fast Output (FWHM) ^{a)}		<0.6ns	1.2ns		3.2ns	
Microcell recovery time ^{a) b)}		180ns	180ns	350ns	210ns	
Temperature dependence of VBr		21.5mV/°C				



X18 package option



X13 package option



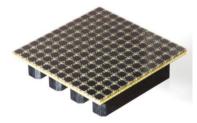
SMT package option



4 SMT Array Variants Available Now



8x8 of 1mm (2.49 cm²)



12x12 of 3mm (25.2 cm²)

1.1	- to to to
-	
-	
	a la la la

4x4 of 3mm (2.74 cm²)

			-	-	-
 			-	-	
 		-	-		
-	A second			-	

8x8 of 6mm (32.94 cm²)

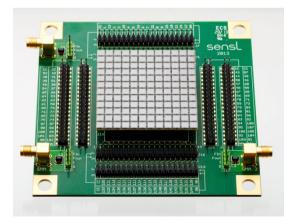
- Available for rapid testing
 - 8x8 of 1mm SMT
 - 1.7mm pitch
 - 4x4 of 3mm SMT
 - 4.2mm pitch
 - 12x12 of 3mm SMT
 - 4.2mm pitch
 - 8x8 of 6mm SMT
 - 7.2mm pitch
- Passive Breakout Board (BoB)
 - Ability to readout any pixel (no amp)
 - 3 SMA connection options
- Full Reference Design Available



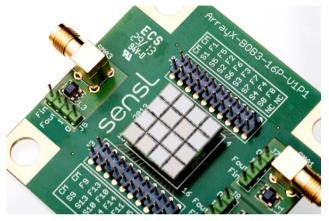
SMT Array Breakout Boards



8x8 of 1mm (2.49 cm²)



12x12 of 3mm (25.2 cm²)



4x4 of 3mm (2.74 cm²)



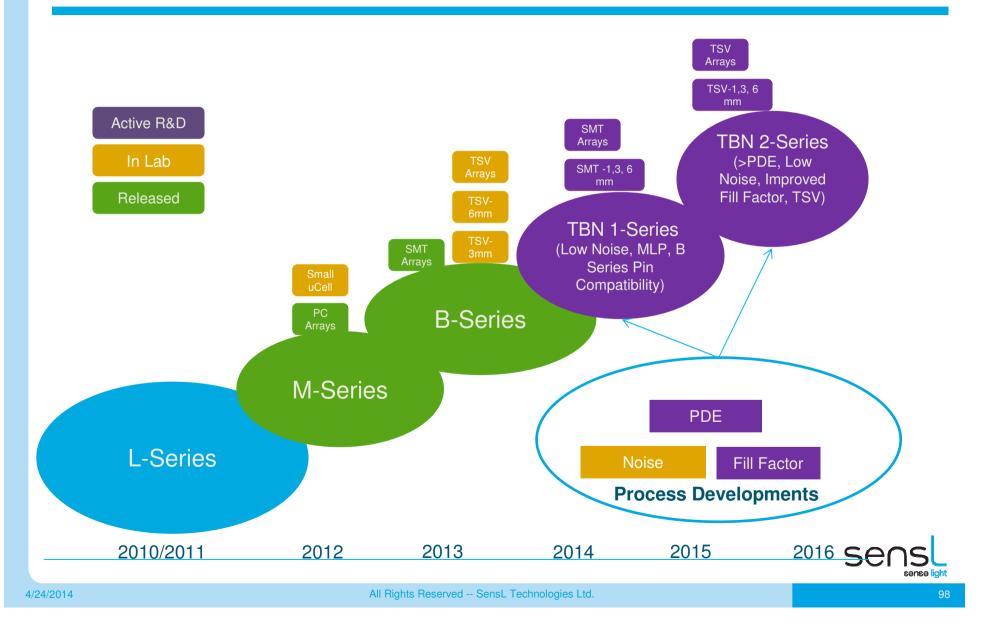
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Roadmap

- Low Noise
- TSV



SiPM Product Roadmap and R&D Plan



Roadmap Summary -- At Glance

TBN-1 Serie	es (Low	Noise)
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MLP/SMT 100% pin & package compatible with B Series
100kHz dark rate/mm² dark noise (20x reduction over B-Series)
Slight shift in Vbr for optimum PDE but otherwise all other B Series attributes

Availability:

- Samples to select customers now (TO Package on SMA board)
- Volume release in MLP/SMT in summer 2014

TBN-2 Series (↑PDE, ↑FF, ↓noise)

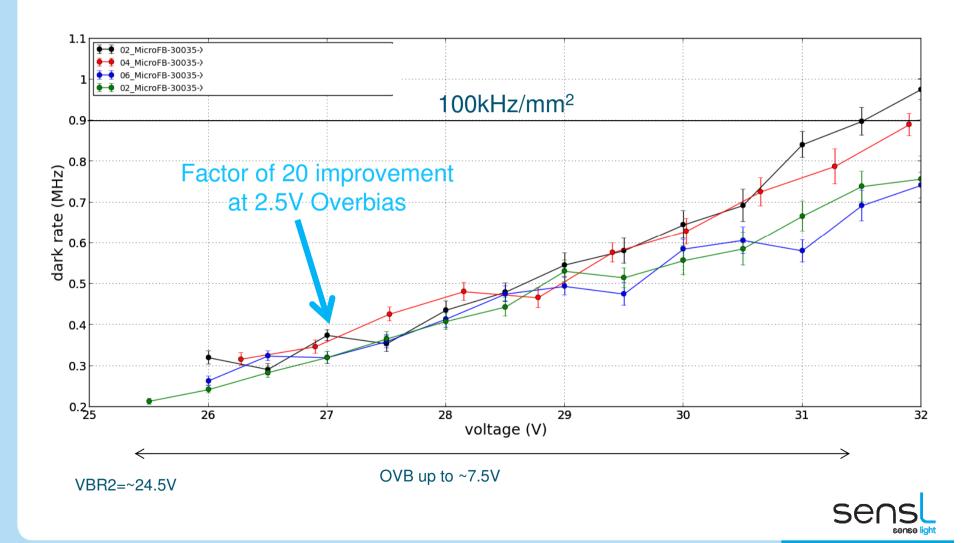
Improved PDE (~50% target) over B Series
Improved fill factor with microcell pitch change

- TSV/SMT package
 - Improved array pitch
 - MSL-1
- •Availability:
 - Samples of TSV/SMT package on SMA board in April (B Series process)
 - Beta samples in Q4 2014
 - General release (Volume) Q1 2015

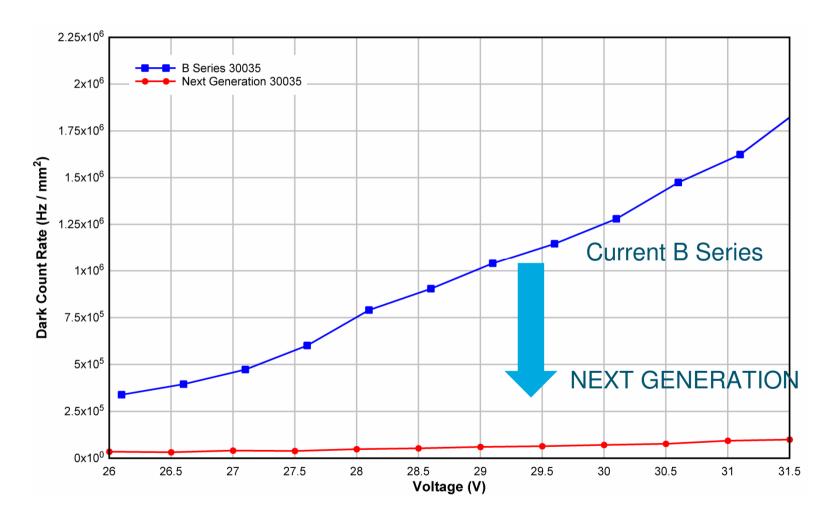


Dark Rate (Measured Lab Results)

February 2014 Process

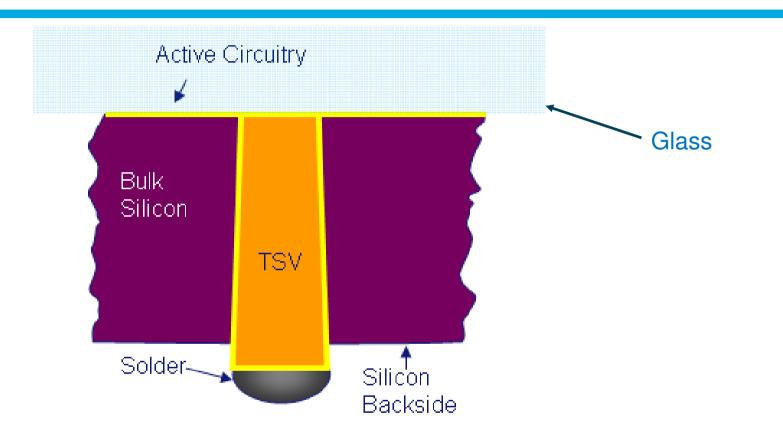


Dark Count - 30035 Engineering Samples



SEAS

Through Silicon Via (TSV)

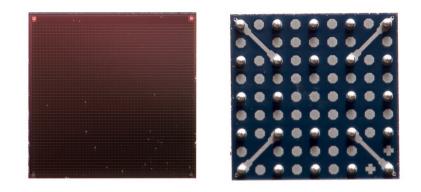


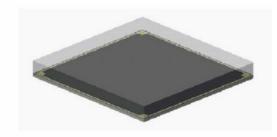
Silicon wafer is attached to glass, thinned to <0.10mm, contact vias are etched, filled and solder balls attached



TSV Package

- Advantages
 - High volume
 - Medium cost
 - Reliability (no wire bonds)
 - Reproducibility
 - Long service life
 - Yield
 - Operating temperature range (-40C to 95C)
 - MR compatible
 - Glass enables best low wavelength PDE
 - Suitable for arrays
 - Large area packages are possible
 - Optimum fill factor
 - MSL1
- Disadvantages
 - Cost of product development
 - Higher unit cost than SMT





<u>Top View</u>



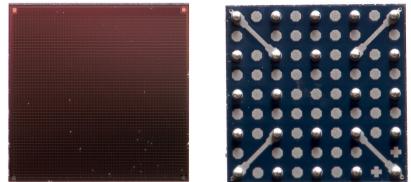
Bottom View



TSV Package Development Status @ SensL

- Devices Currently in lab (B Series Process)
 - 1mm
 - 3mm
 - 6mm
- Demonstrates package concept and reduces risk to TBN-2 Series significantly



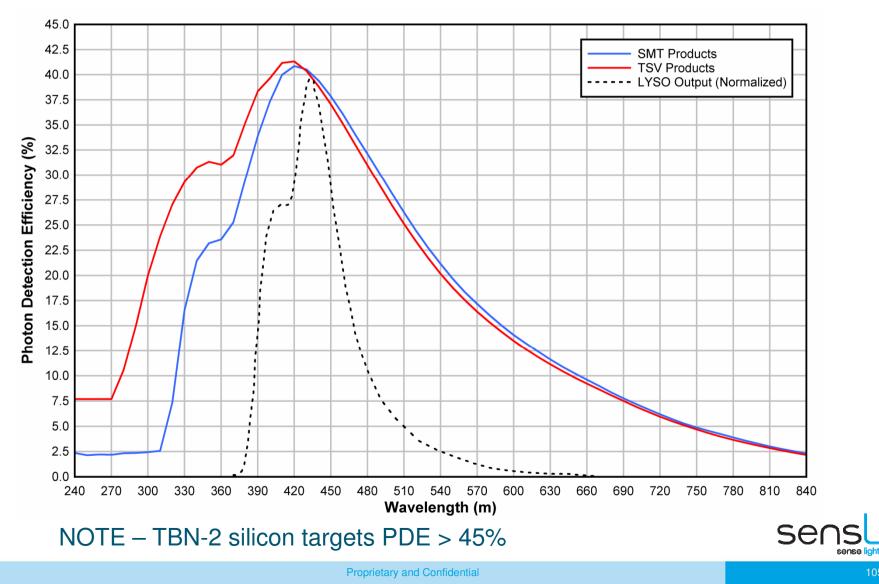


SensL TSV Devices





TSV <u>B-Series</u> PDE (35um Microcell)





Спасибо!



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